



Graphene based mid-infrared and THz devices and their potential application in astronomical instruments

Christiano J. S. de Matos

MackGraphe

Mackenzie Presbyterian University, Brazil



About MackGraphe



MackGraphe

(Graphene and Nanomaterials Research Center)



- A center dedicated to the science and industrial application of graphene and other 2D materials
- Began its activities in 2013
- Headquarters building opened on 2 march 2016
 - 9-storey building
 - Class 1000 clean room
 - Photonics, chemistry, materials labs
 - Space for spin off companies
- 3 areas of interest: Photonics, Energy, Composite Materials



Talk outline

- Graphene
 - Basics
 - Fabrication
 - Electronic/optoelectronic/plasmonic properties
- Graphene devices for THz technologies
 - Antennas
 - Detectors
 - Filters/polarizers
- Conclusions and outlook



What is graphene?

- A 1 atom thick sheet composed of sp^2 carbon atoms assembled in a hexagonal crystal lattice
- The world's first (**but not only**) 2D material





Graphene: a superlative material

The thinnest material

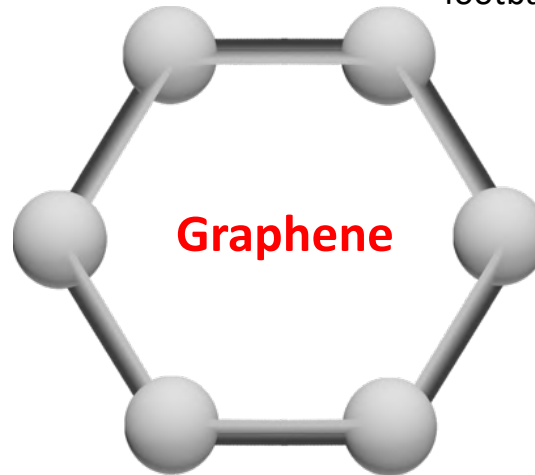
A million times thinner than a human hair and, therefore, flexible.

The lightest material

3 gram of graphene covers a football field.

The highest thermal conductivity

10 times higher thermal conductivity than in copper.



Transparent

Graphene absorbs only 2.3% of incident light. It is, therefore, almost invisible to naked eye.

The best electricity conductor

The best known electricity conductor.

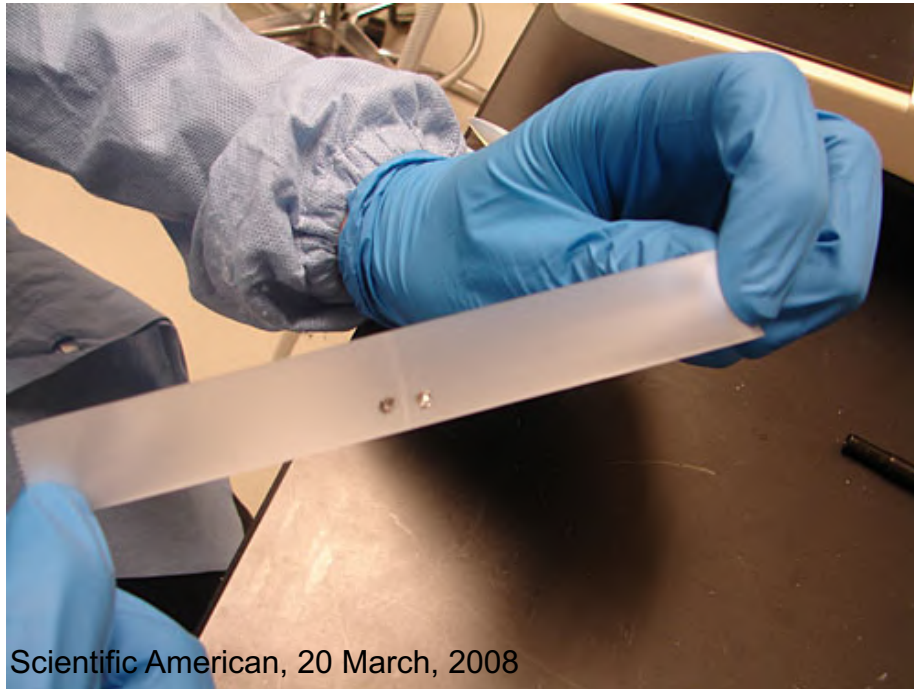
The strongest material

>200 times stronger than steel.

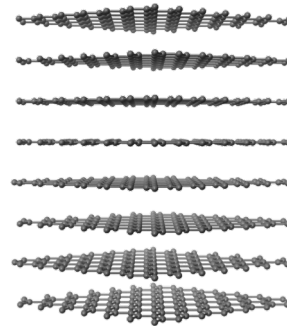


MackGraph

Obtaining graphene from graphite: mechanical exfoliation



Scientific American, 20 March, 2008



Graphene

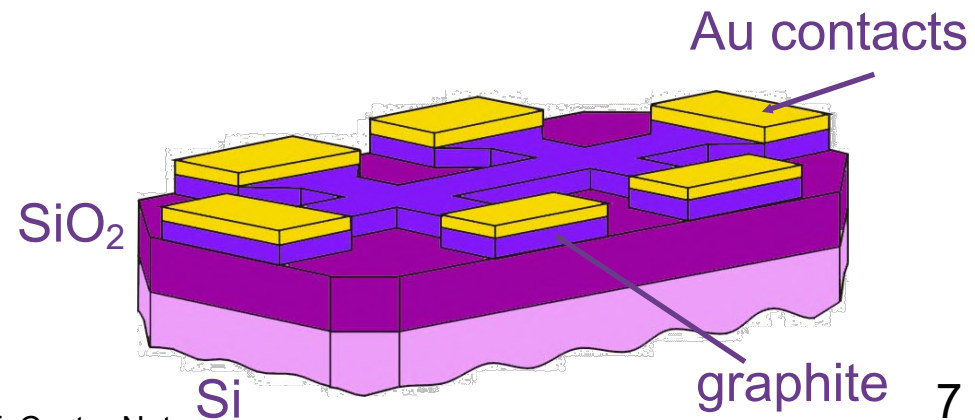




The first electronic circuits



- optical image
- SEM image
- design
- contacts and mesa





Other 2D materials



Two-dimensional atomic crystals

K. S. Novoselov*, D. Jiang*, F. Schedin*, T. J. Booth*, V. V. Khotkevich*, S. V. Morozov†, and A. K. Geim**

*Centre for Mesoscience and Nanotechnology and School of Physics and Astronomy, University of Manchester, Manchester M13 9PL, United Kingdom; and †Institute for Microelectronics Technology, Chernogolovka 142432, Russia

Edited by T. Maurice Rice, Swiss Federal Institute of Technology, Zurich, Switzerland, and approved June 7, 2005 (received for review April 6, 2005)

We report free-standing atomic crystals that are strictly 2D and can be viewed as individual atomic planes pulled out of bulk crystals or as unrolled single-wall nanotubes. By using micromechanical cleavage, we have prepared and studied a variety of 2D crystals including single layers of boron nitride, graphite, several dichalcogenides, and complex oxides. These atomically thin sheets (essentially gigantic 2D molecules unprotected from the immediate environment) are stable under ambient conditions, exhibit high crystal quality, and are continuous on a macroscopic scale.

PNAS

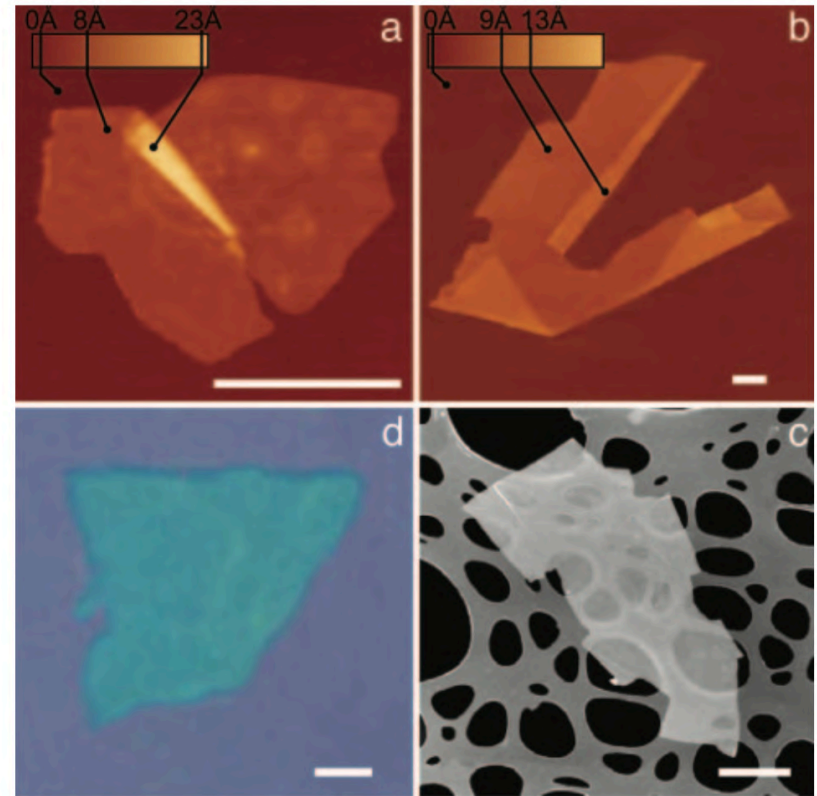


Fig. 1. 2D crystal matter. Single-layer crystallites of NbSe₂ (a), graphite (b), Bi₂Sr₂CaCu₂O_x (c), and MoS₂ (d) visualized by AFM (a and b), by scanning

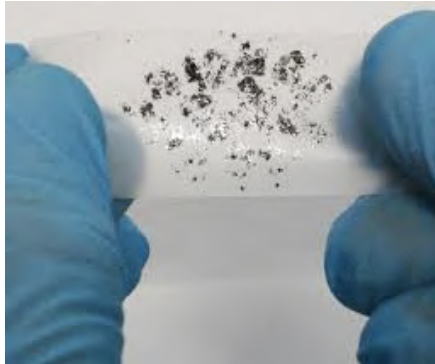


Ways to obtain graphene



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Mechanical exfoliation



Crystal quality: highest

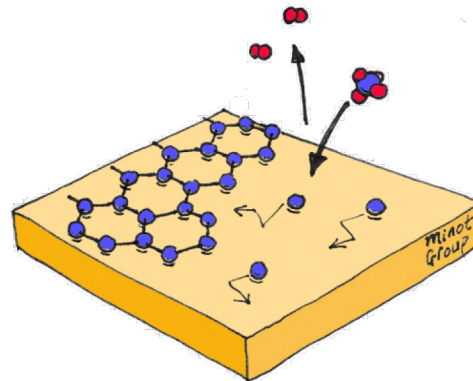
Scalability: low

Continuous area: small

Total area: small

Interaction w/ environment: low

Chemical vapor deposition



From Minot Group – Oregon State Univ.

Crystal quality: medium/high

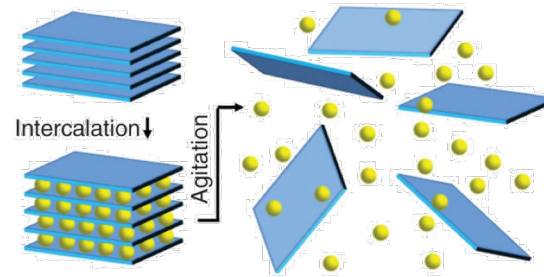
Scalability: medium

Continuous area: large

Total area: small/medium

Interaction w/ environment: low

Chemical/liquid assisted chemical exfoliation



Nicolosi et al., Science 340, 419, 1226419 (2013)

Crystal quality: low/medium

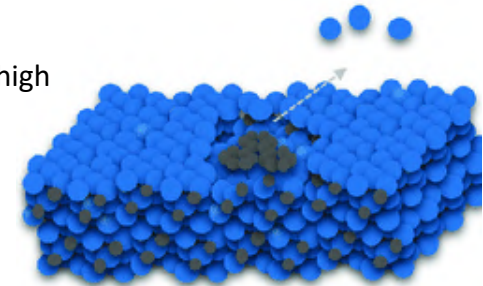
Scalability: high

Continuous area: small

Total area: large

Interaction w/ environment: high

Epitaxial growth



● Carbon ● Silicon

Zhao et al., Chem Soc Rev 46, 4417 (2017)

Quality: high

Scalability: medium/high

Continuous area: large

Total area: small

Interaction w/ environment: low



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Obtaining graphene in a larger scale: chemical vapor deposition

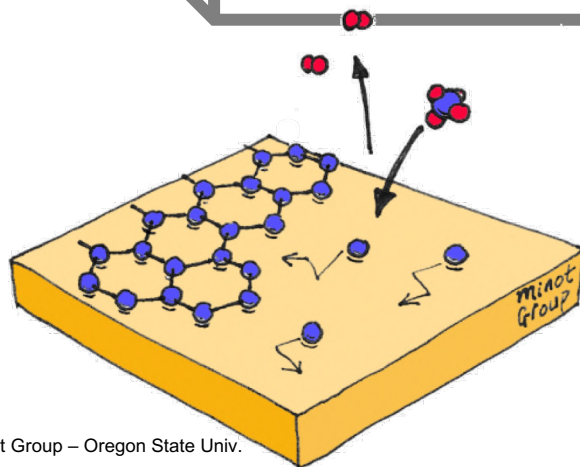


Oven

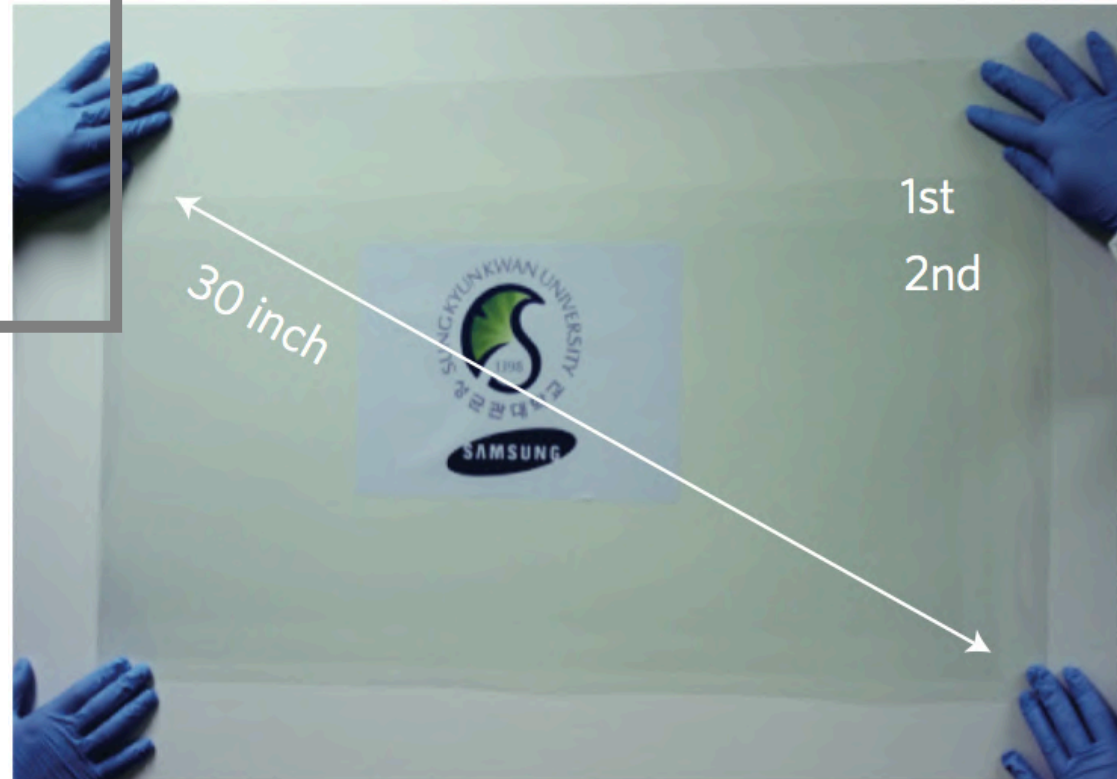
CH_4



Copper foil

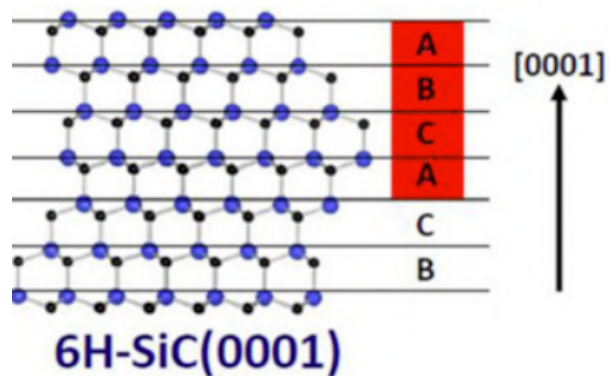


From Minot Group – Oregon State Univ.

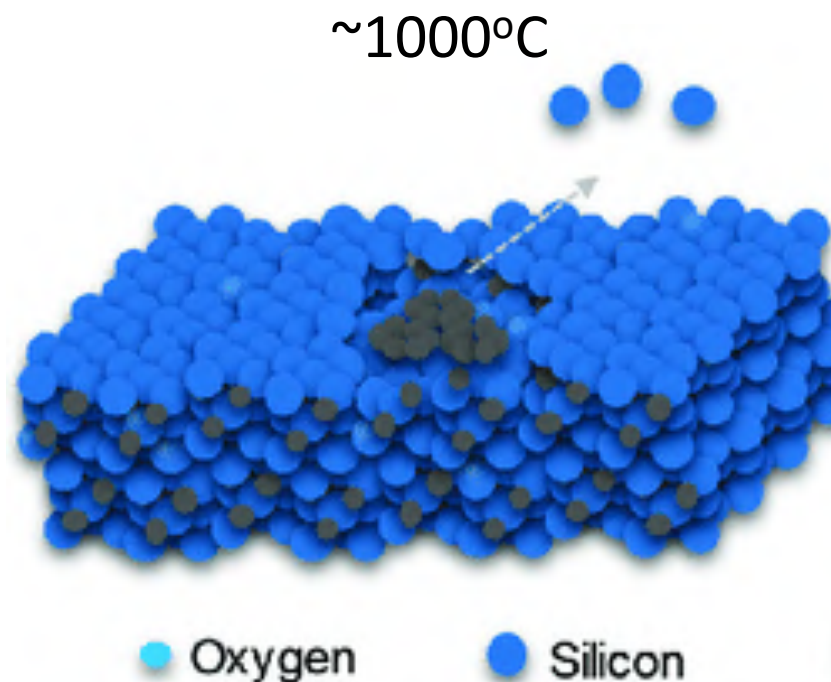




Obtaining graphene in a larger scale: epitaxial growth



Otsuji et al., J. Phys D 45, 303001 (2012)

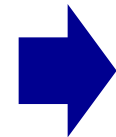
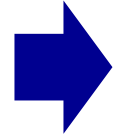
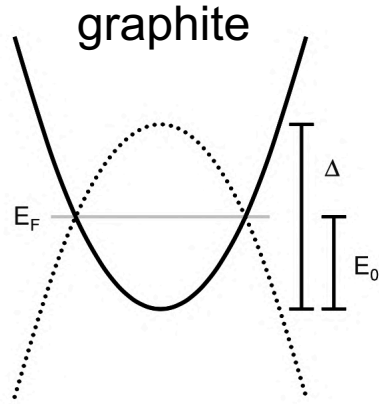


Zhao et al., Chem Soc Rev 46, 4417 (2017)

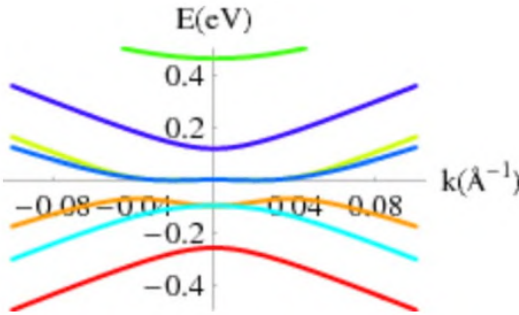


Dimensionality reduction: consequences to electrons

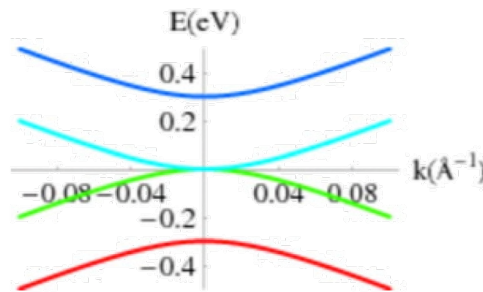
Changes in the band structure



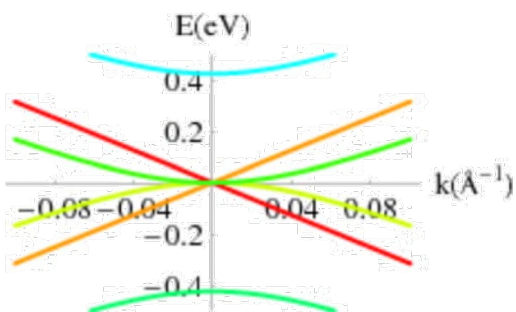
4 layers



2 layers



3 layers



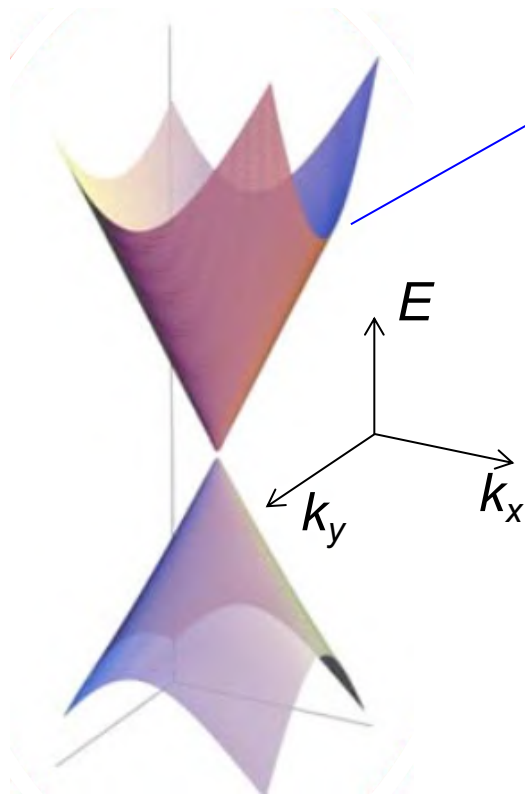
graphene





Dimensionality reduction: consequences to electrons

Linear (conical) dispersion relation, instead of parabolic



$$E(k) = \hbar v_F k$$

v_F (electron's phase velocity) is independent of E

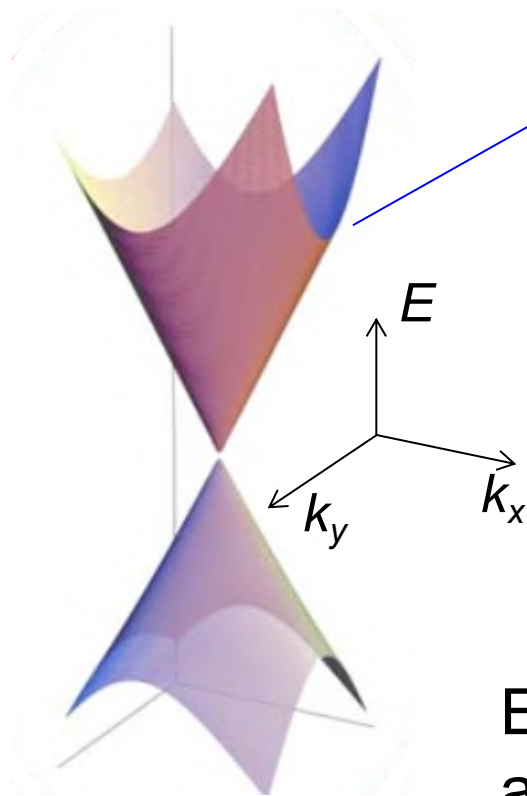
In a material with an usual (parabolic) dispersion

$$v = \sqrt{\frac{2E}{m}}$$



Conical dispersion: consequences to electrons

Linear (conical) dispersion relation, instead of parabolic



$$E(k) = \hbar v_F k$$

In which other situation fermions exhibit E proportional to k ?

Relativistic dispersion with $m = 0$

$$E(k) = \sqrt{\hbar^2 k^2 c^2 + (mc^2)^2} = \hbar ck$$

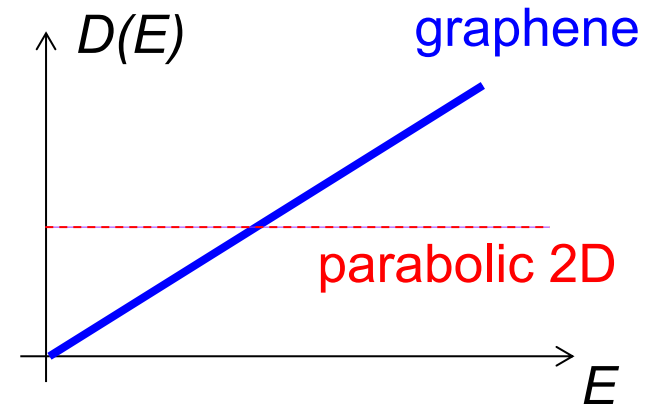
Equations are identical if $v_F \rightarrow c$
and $m^* = 0$ (zero effective rest mass)



Conical dispersion: consequences to electrons

- One consequence of the conical dispersion:
density of states

$$D(E) = \frac{k(E)}{\pi} \frac{dk}{dE} = \frac{E}{\pi \hbar v_F} \frac{1}{\hbar v_F} = \frac{E}{\pi (\hbar v_F)^2}$$



Electron surface density in the conduction band

$$n_q(E_F) = 2 \int_0^{E_F} D(E) dE = 2 \int_0^{E_F} \frac{E}{\pi (\hbar v_F)^2} dE = \frac{E_F^2}{\pi (\hbar v_F)^2} = \frac{k_F^2}{\pi}$$

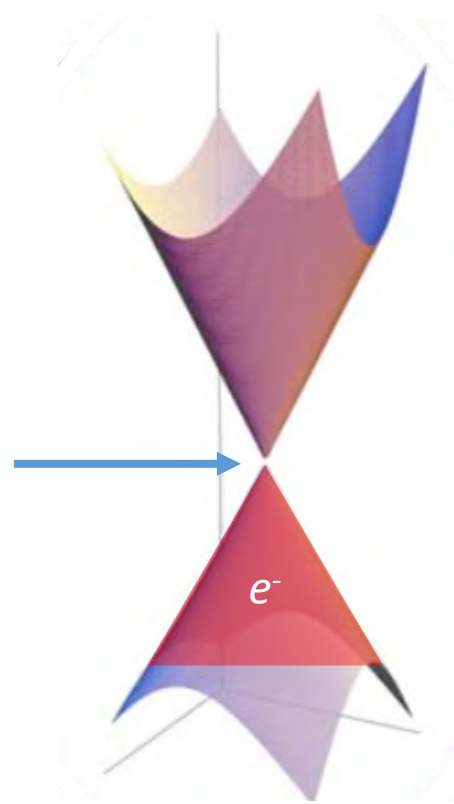
(factor 2 accounts for 2 1BZ points contributing)

$$E_F = \hbar v_F \sqrt{\pi n_q}$$



- Doped graphene versus neutral graphene

Neutrality point
 $E_F = 0$

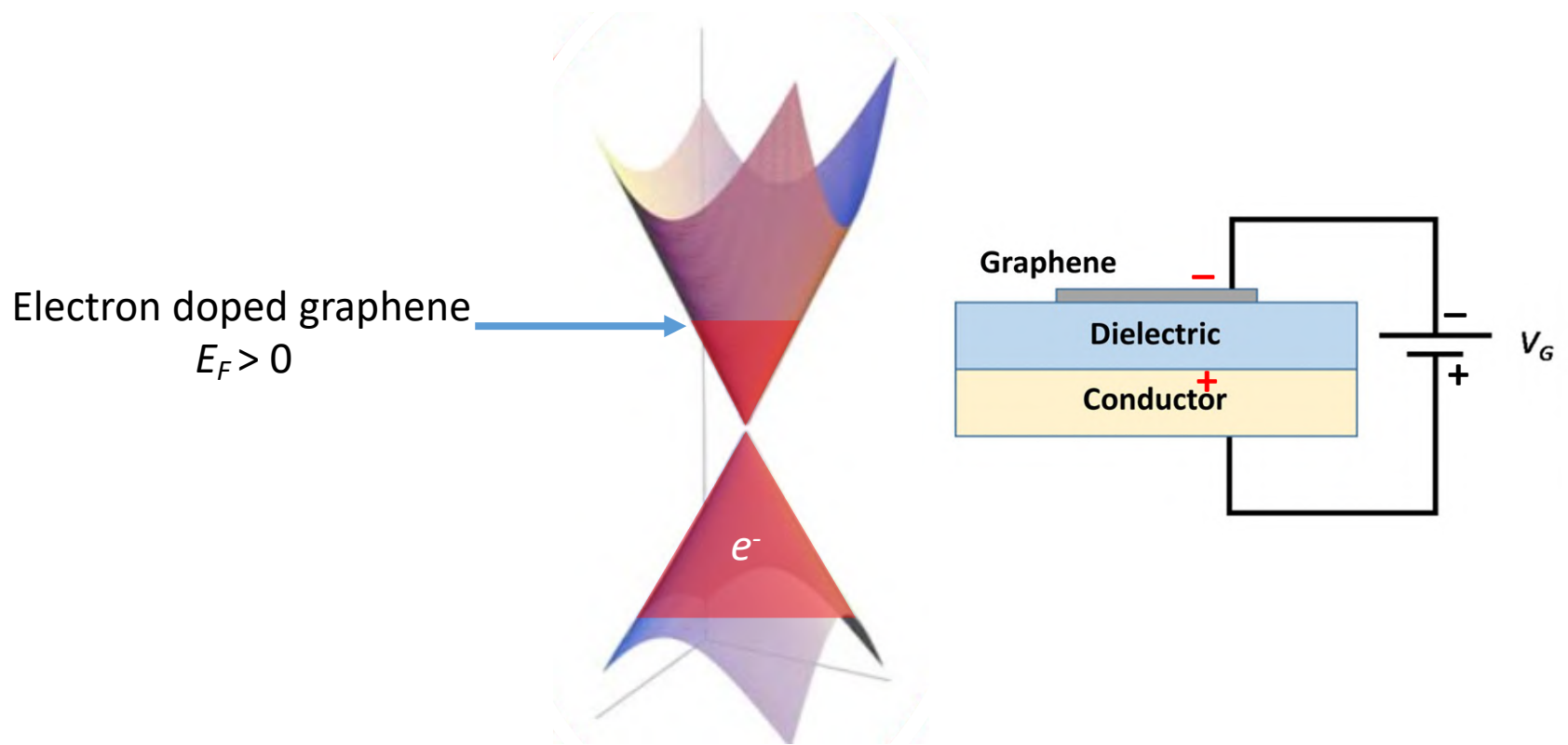




Electrical doping of graphene



- Doped graphene versus neutral graphene

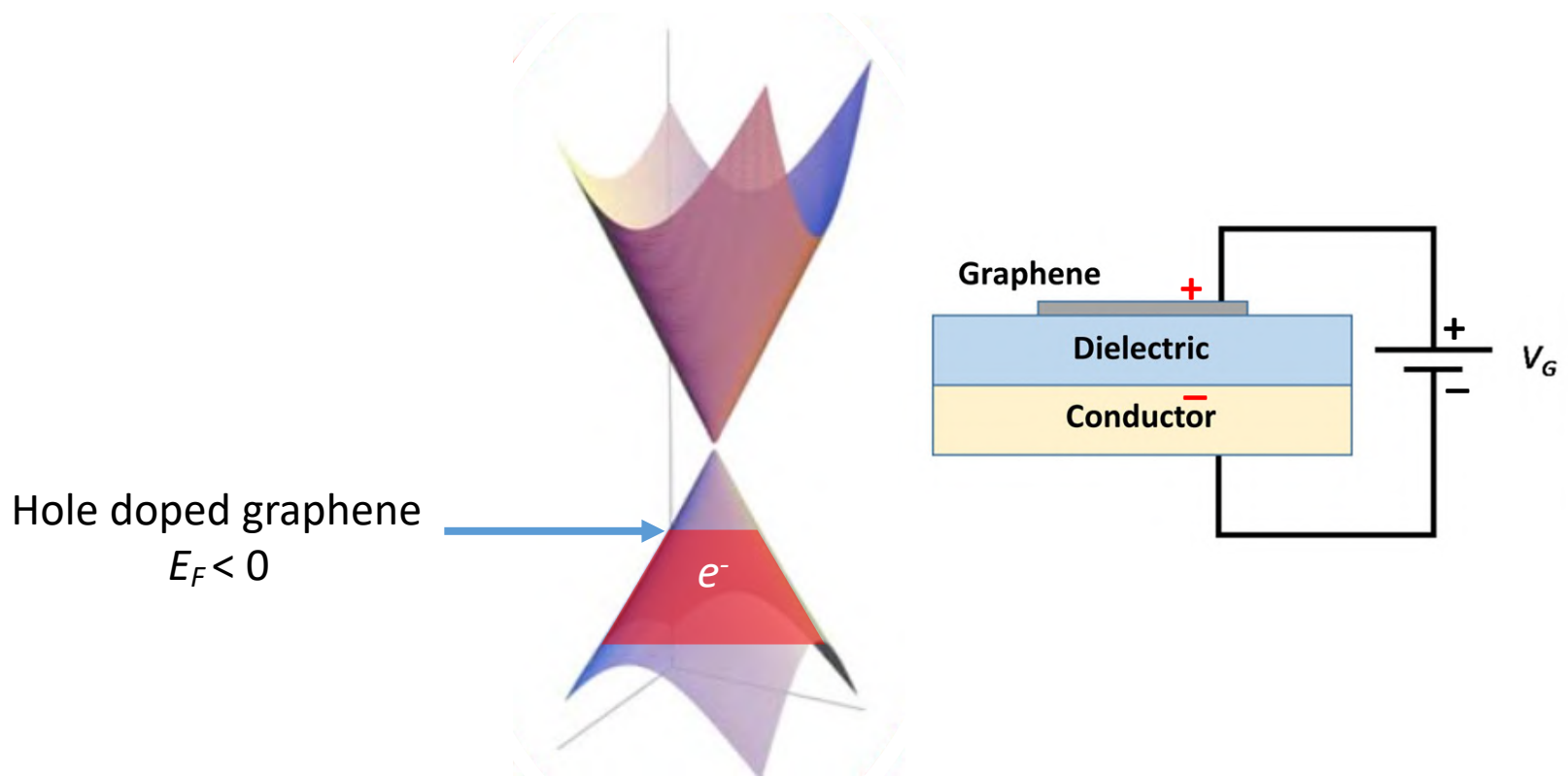




Electrical doping of graphene



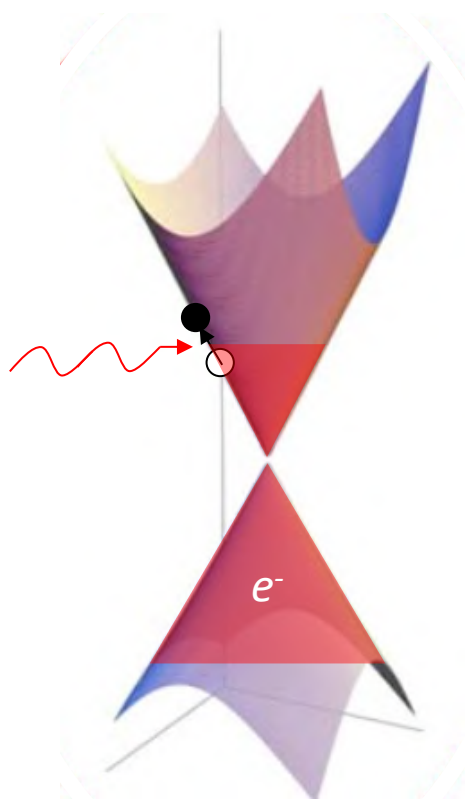
- Doped graphene versus neutral graphene



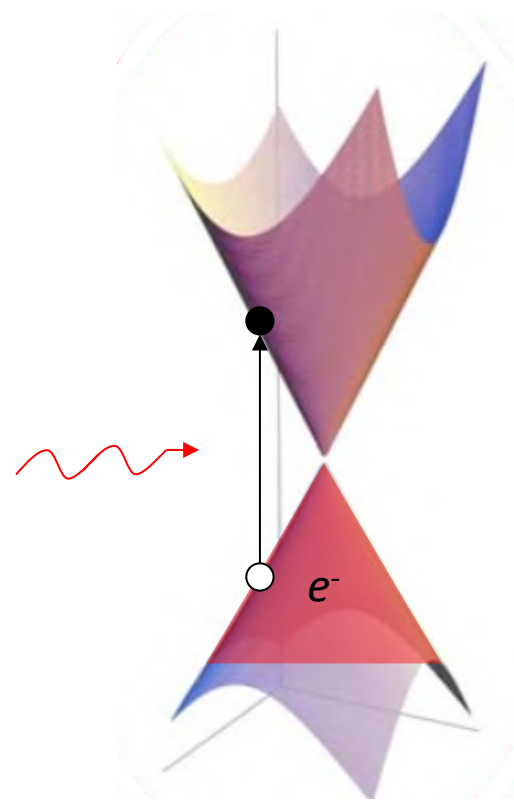


Intraband transition versus interband transition

intraband transition



interband transition





Intraband transition versus interband transition

- We can, therefore, see that there will be an intraband and an interband optical conductivity:

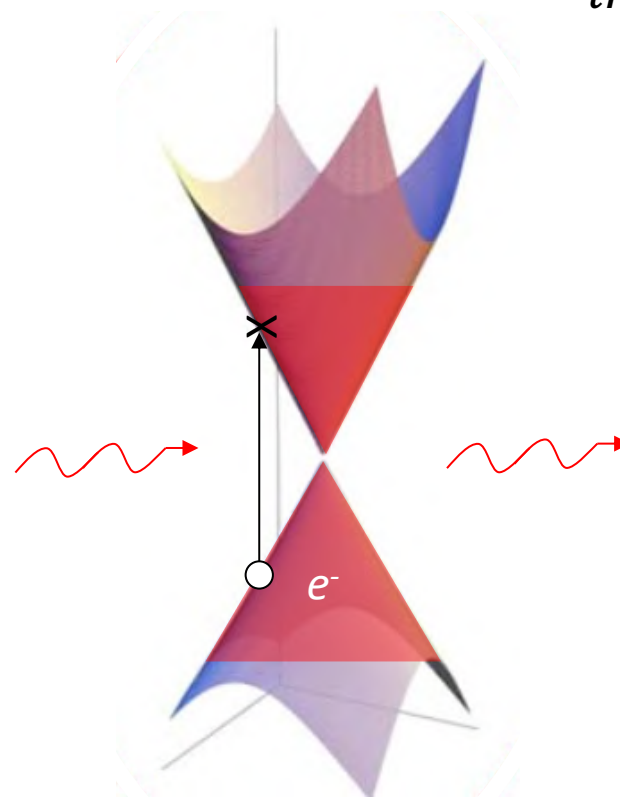
$$\sigma(\omega) = \sigma_{intra}(\omega) + \sigma_{inter}(\omega)$$



Interband transition: Pauli blocking

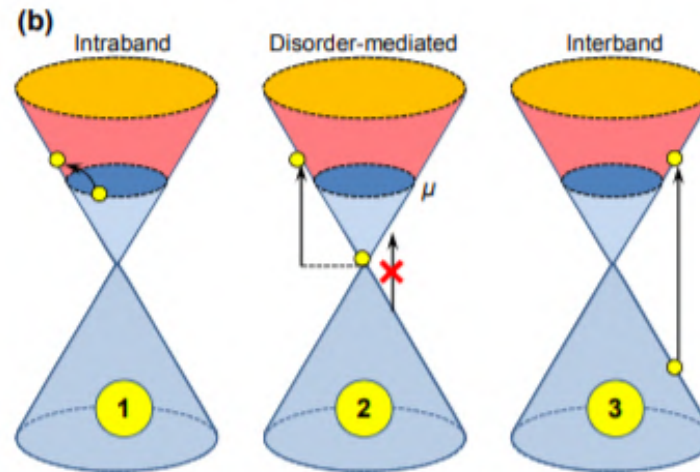
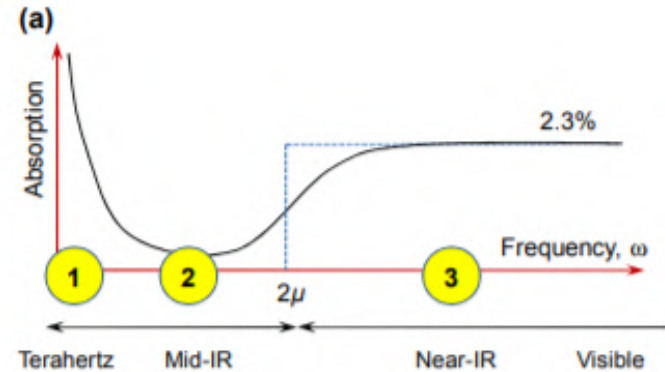
- When $\hbar\omega < 2E_F$: the Pauli exclusion principle prevents interband transition $\rightarrow \sigma_{inter} \rightarrow 0$

interband transition





Dielectric tunability

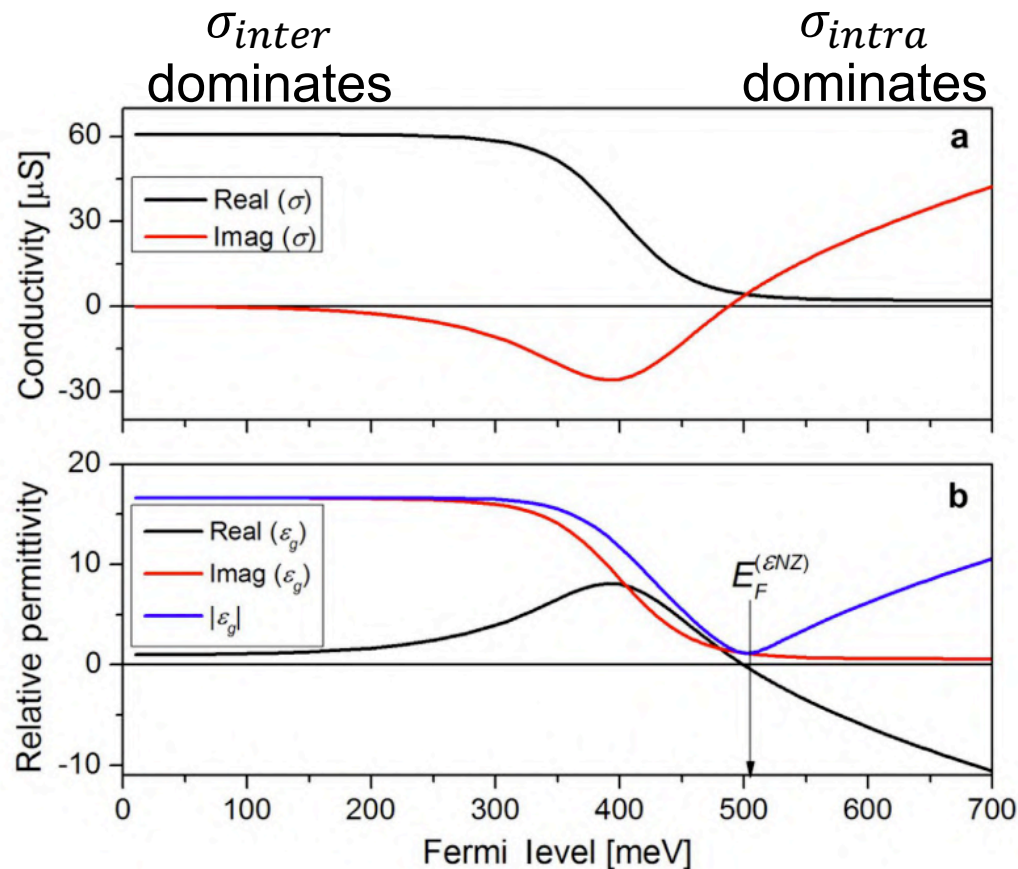


Low and Avouris, *ACS Nano* 8, 1086 (2014)



Dielectric tunability

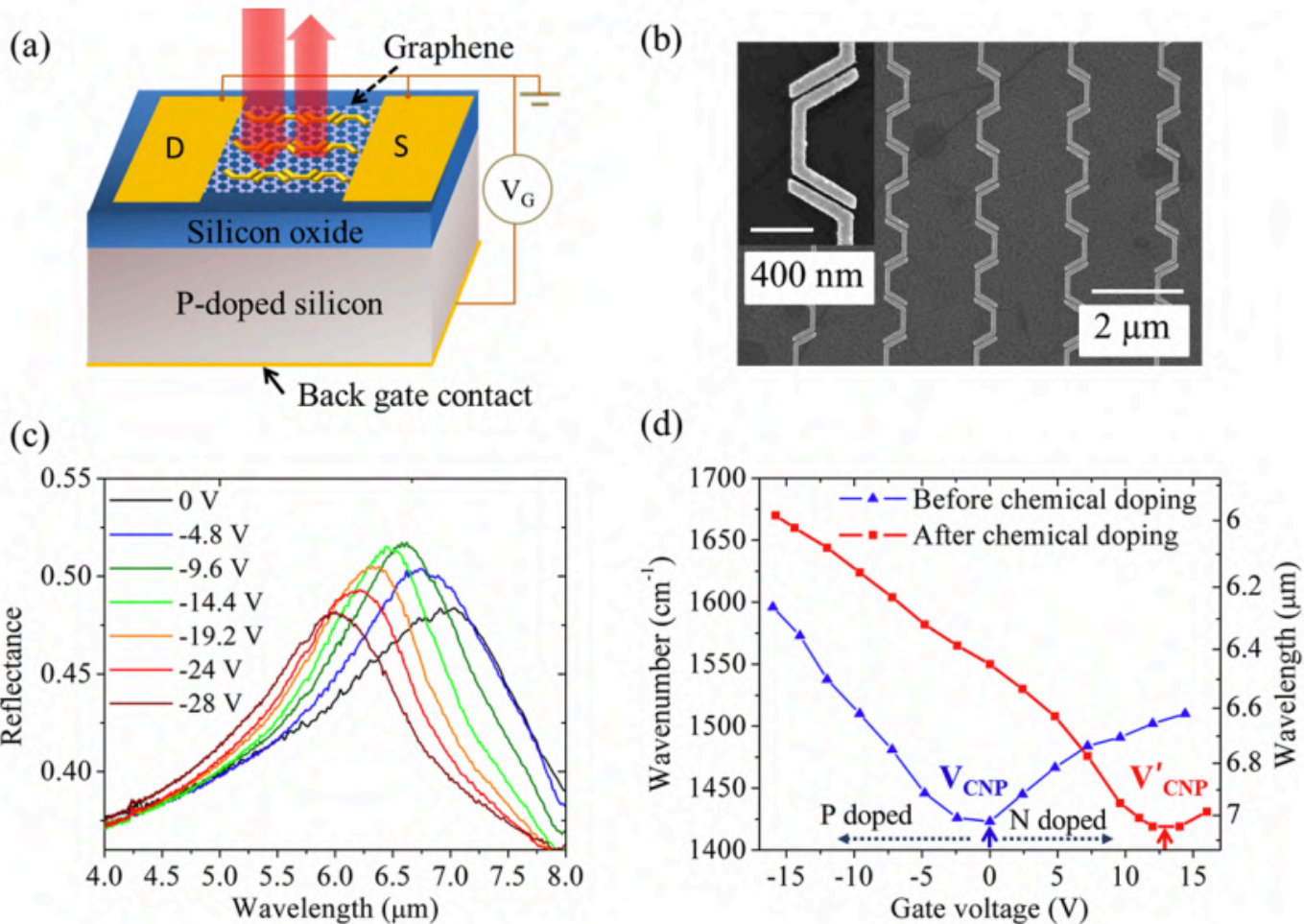
- $\epsilon_g = 2.5 + i\sigma/(\omega\epsilon_0 t_g)$
- Drastic dielectric function tunability



$\hbar\omega = 800$ meV



Spectral tunability in graphene loaded antennas



Yao et. al, Nano Lett. 14, 214 (2004).

- Bias induced changes in graphene's dielectric function in the metal gaps tune the spectral response



Intraband conductivity

- σ_{intra} gives graphene its conductive character, and it can be approximated by the Drude conductivity.
- The (intraband) Drude conductivity is given by

$$\sigma(\omega) = \frac{n_q e^2 \tau}{m(1 - i\tau\omega)}$$

- For graphene, we can write

$$m = \frac{\hbar k}{v_F} = \frac{E_F}{v_F^2} = \frac{\hbar \sqrt{\pi n_q}}{v_F}$$

- So that:

$$\sigma(\omega) = \frac{v_F e^2 \tau \sqrt{n_q}}{\hbar \sqrt{\pi} (1 - i\tau\omega)}$$



Intraband conductivity

- In a parabolic dispersion 2D material:

$$m = \left(\frac{d^2 E}{dp^2} \right)^{-1} = c_1 \hbar^2$$

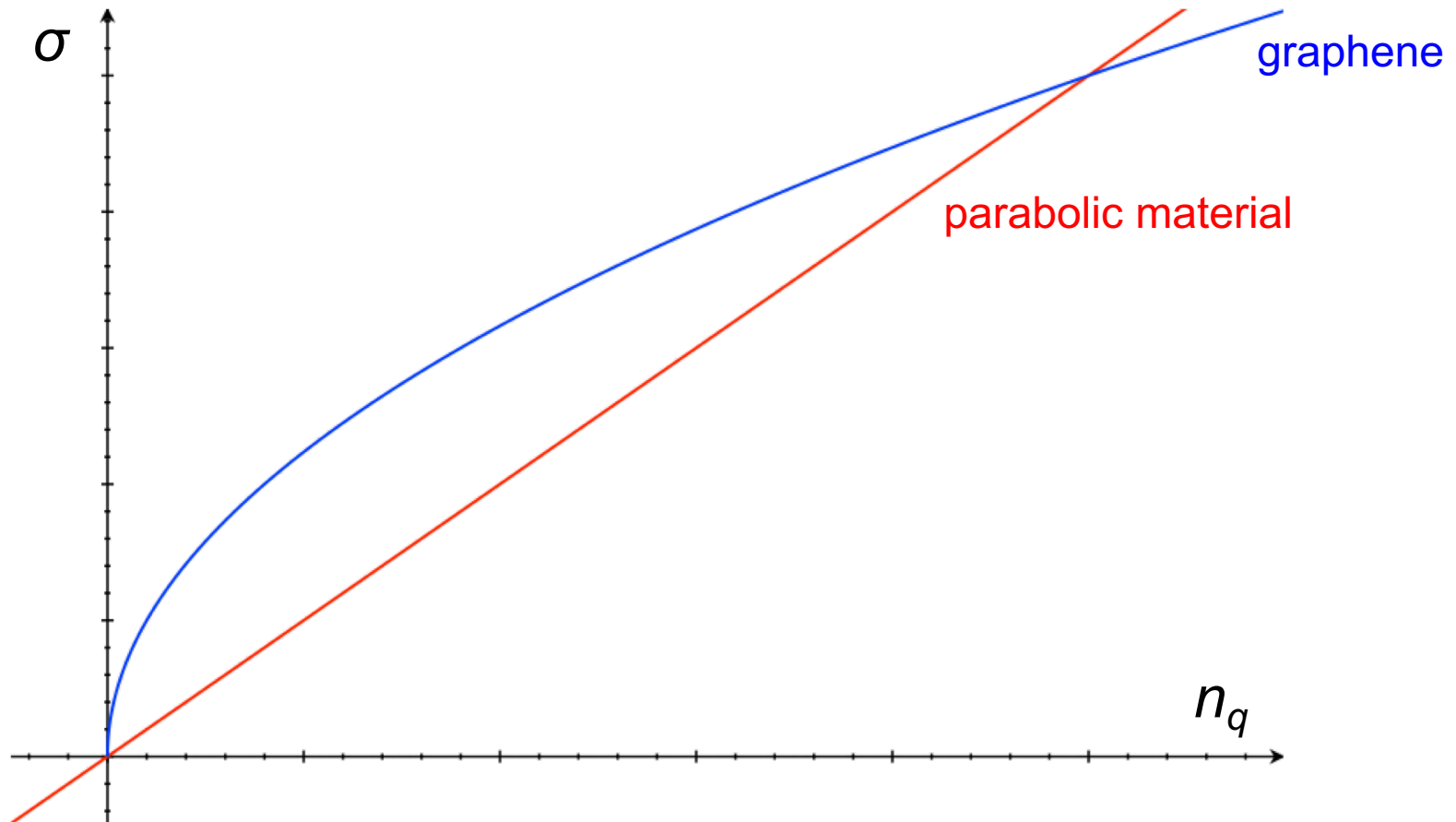
constant

- And therefore

$$\sigma(\omega) \propto \frac{e^2 \tau n_q}{\hbar^2 (1 - i\tau\omega)}$$



Intraband conductivity

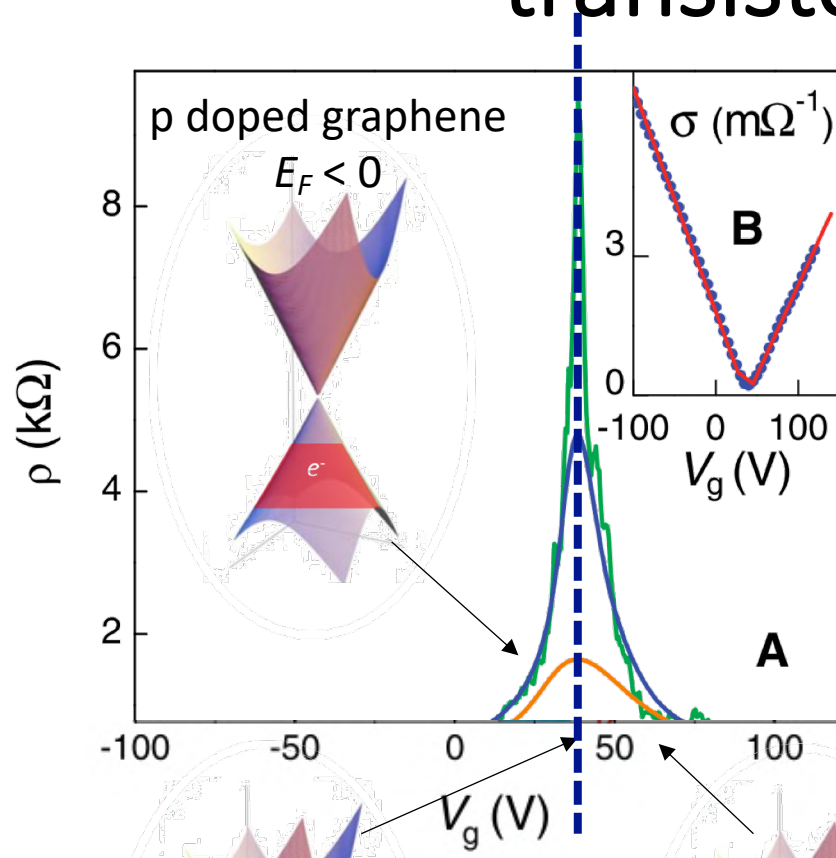


- Over relevant n_q values, graphene's conductivity tunes much more than that of parabolic 2D materials



Graphene field effect transistors (GFETs)

Novoselov et. al, Science 305, 666 (2004).



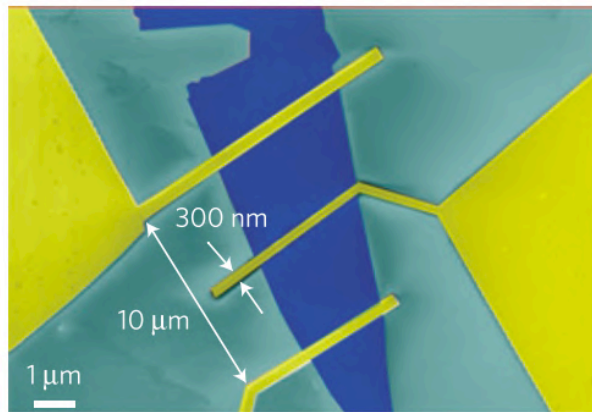
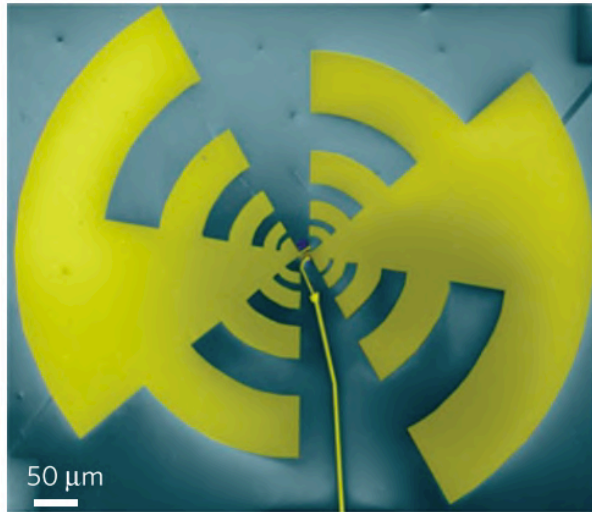
- Ambipolar behavior
- 2D field effect electronic and optoelectronic devices (logic gates, photodetectors, ...)
- Very high charge mobility (ballistic charge movement)

Undoped graphene
 $E_F = 0$

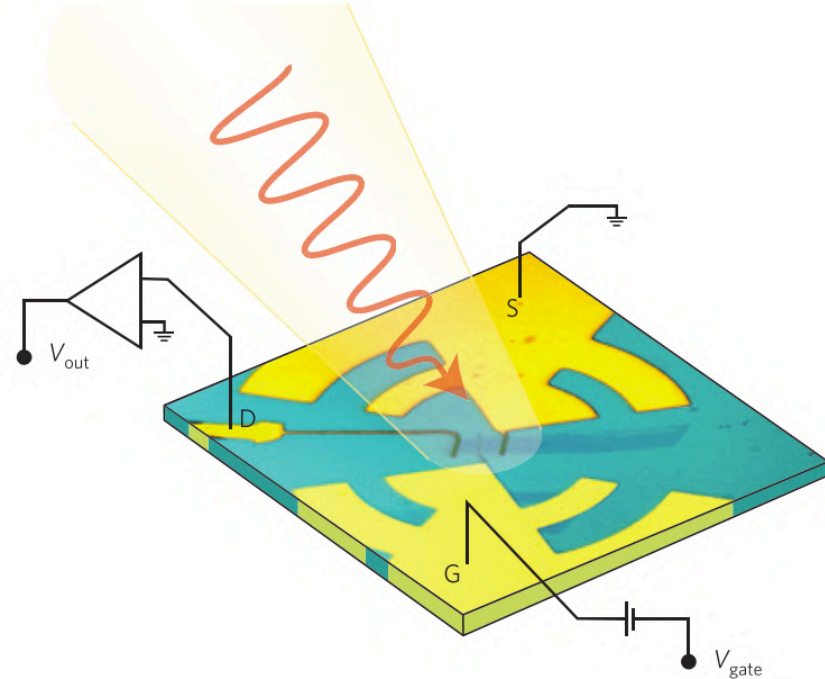
n doped graphene
 $E_F > 0$



GFETs as room temperature THz detectors



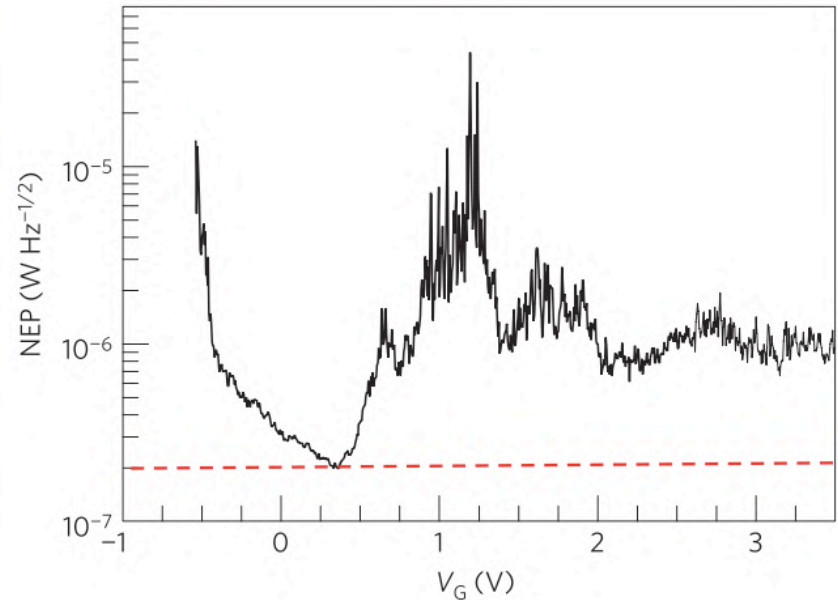
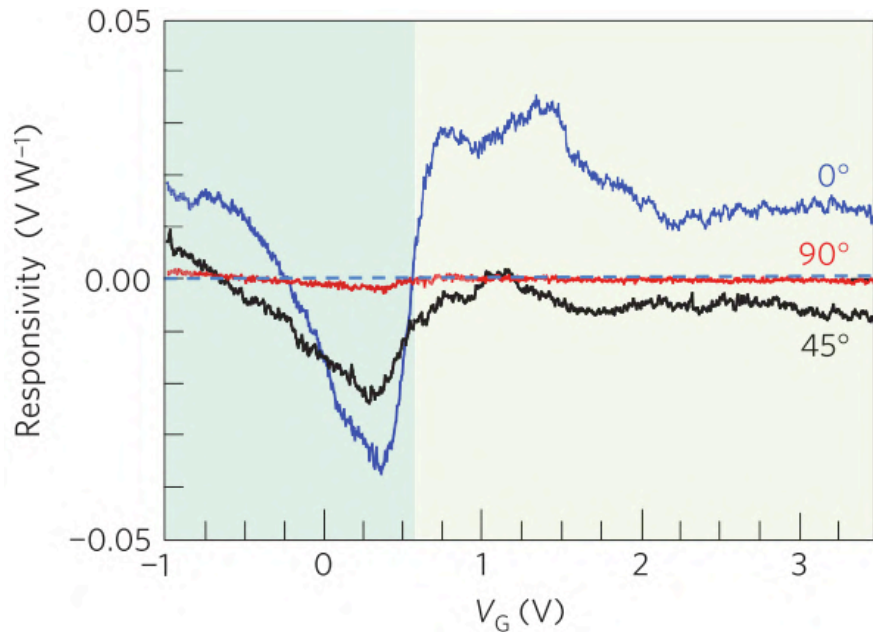
Vicarelli et. al, Nature Mat. 11, 865 (2012).



- 2 lobes of a log-periodic circular toothed antenna connected to the source and top gate
- Incoming fields modulate charge density
- Non-resonant response
- A nonlinearly rectified V_{sd} generated the detected signal



GFETs as room temperature THz detectors



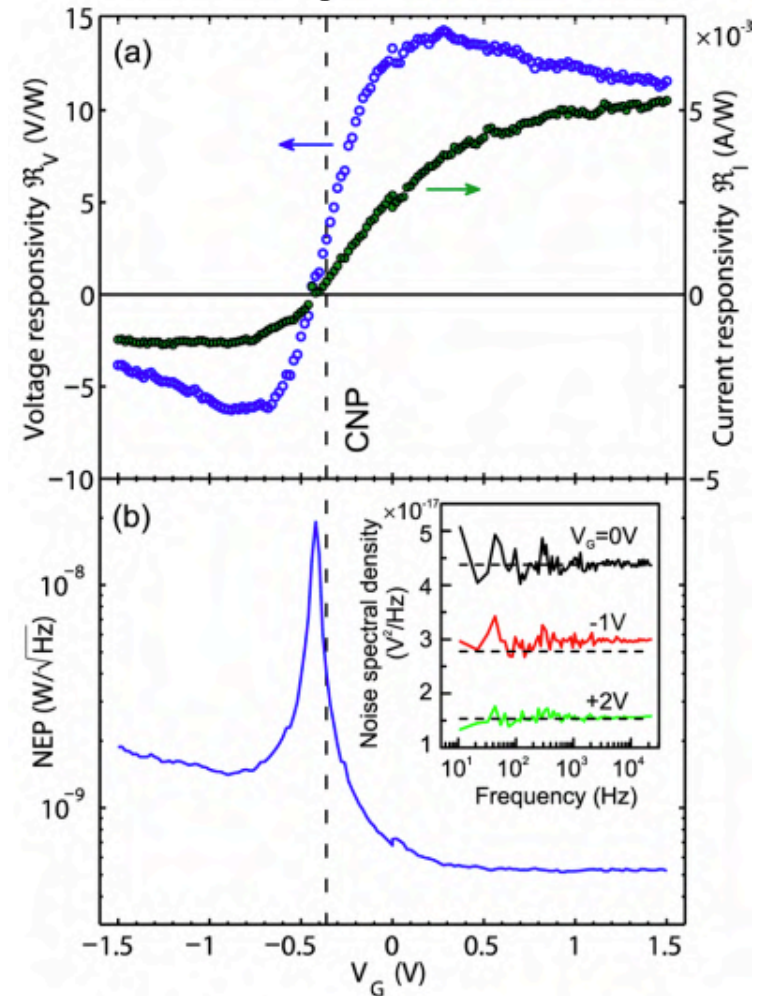
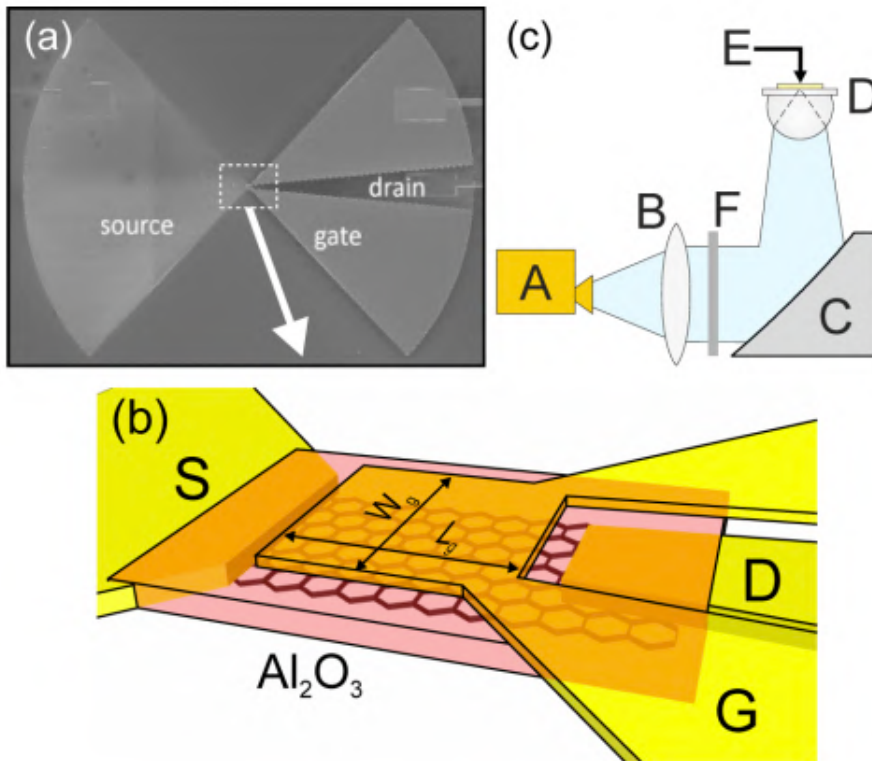
- Tests @ 0.3 THz, but broadband operation expected
- Noise equivalent power limited by the (improvable) charge mobility in the device
- A device based on bilayer graphene also shown



GFETs as room temperature THz detectors



- A somewhat better performance with CVD graphene



- Tests at 0.6 THz
- R_v up to 14 V/W, NEP as low as $515 \text{ pW}\cdot\text{Hz}^{1/2}$



Heterodyne detection with a graphene bolometric mixer

nature
astronomy

LETTERS

<https://doi.org/10.1038/s41550-019-0843-7>

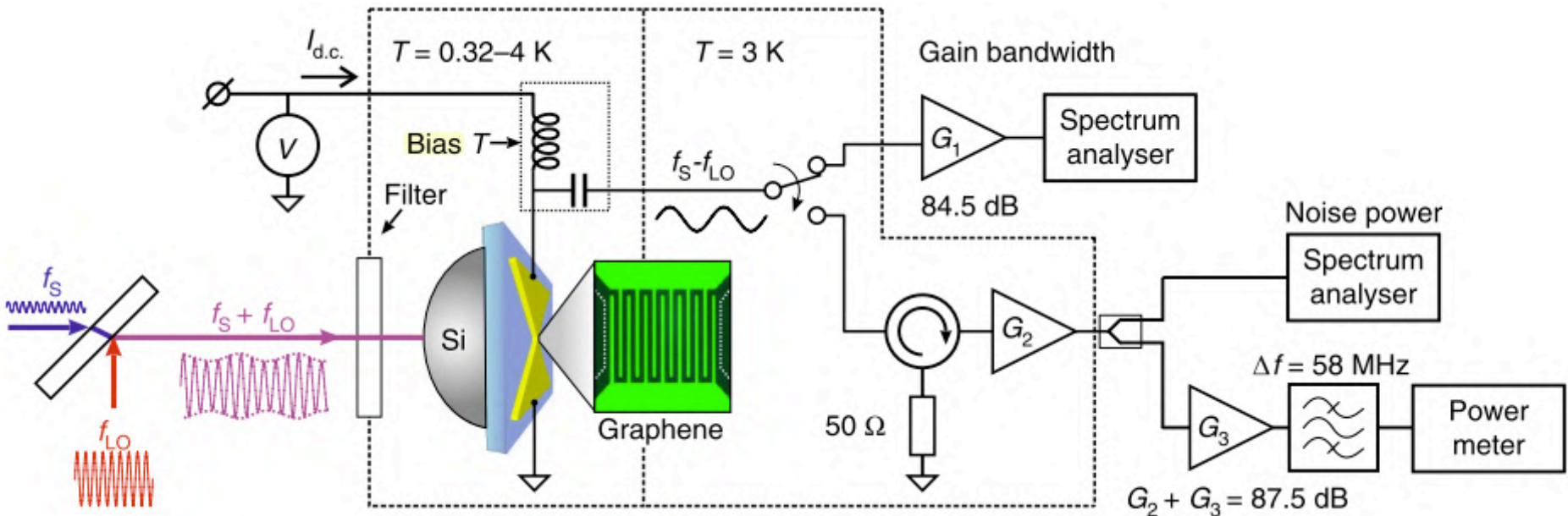
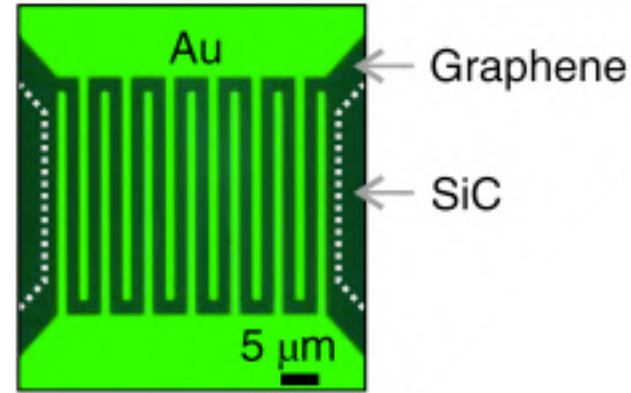
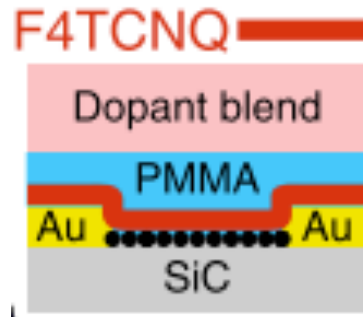
Towards quantum-limited coherent detection of terahertz waves in charge-neutral graphene

S. Lara-Avila^{1,2*}, A. Danilov¹, D. Golubev³, H. He¹, K. H. Kim¹, R. Yakimova⁴, F. Lombardi¹, T. Bauch¹, S. Cherednichenko¹ and S. Kubatkin¹

- For high quality graphene, quantum effects emerge and alter the intraband conductivity of graphene, adding a temperature dependent term: $\sigma_{intra} = \sigma_{Drude} + \sigma_1 \ln(T/1K)$
- The 2nd term is relatively small except for when $n_q \rightarrow 0$ ($\sigma_{Drude} \rightarrow 0$)
- This requires high control over spurious graphene doping

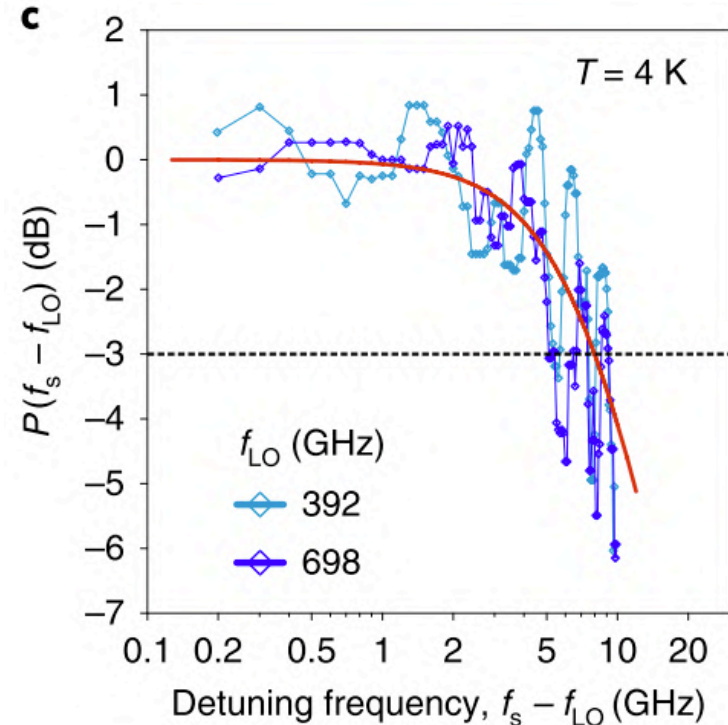
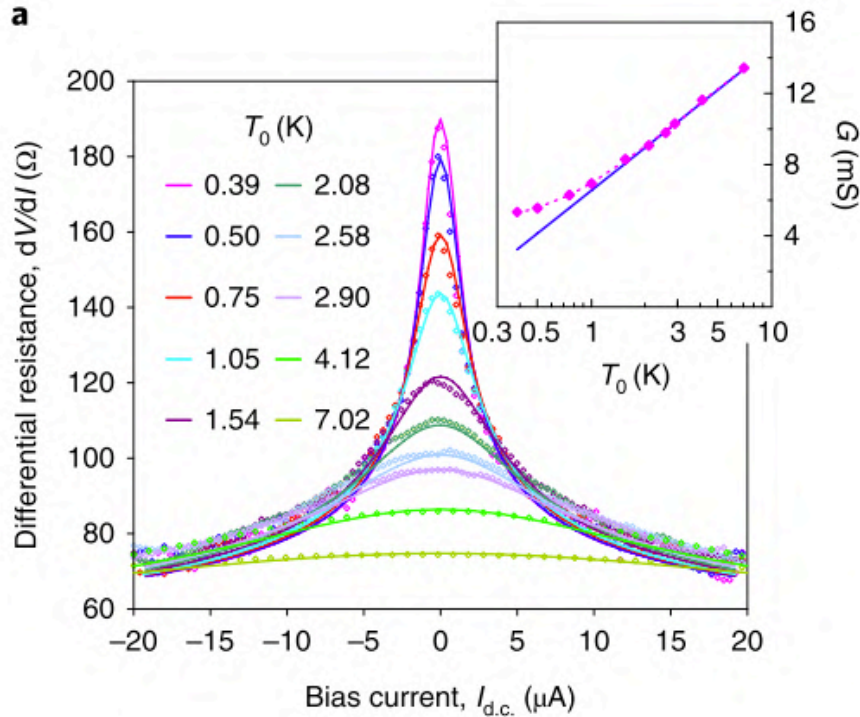


Heterodyne detection with a graphene bolometric mixer





Heterodyne detection with a graphene bolometric mixer



- Ultrafast (~ 20 ps) heat dissipation via hot electron diffusion into the gold leads lead to 8 GHz bandwidth



Heterodyne detection with a graphene bolometric mixer

- Background radiation limits the performance in the lab. Performance in space (~ 0 background) can be predicted:

Table 1 | Summary of graphene bolometric mixer parameters

	L (μm)	f_0 (GHz)	f_{LO} (GHz)	P_{LO} (nW)	$I_{\text{d.c.}}$ (μA)	P_{Bkg} (nW)	T_5 (K)	G_{mix} (dB)	T_{mix} (K)
Measured	1.5	8	98, 392, 698	3.8	5	0.28	1.9	-27	475
Projected	0.8	20	Entire THz range	0.04	1	0	0.4	-22	36 ($T_{\text{Amp}} \sim 0.3\text{ K}$) 125 ($T_{\text{Amp}} \sim 1\text{ K}$)

Lara-Avila et. al, Nature Astronomy (2019).



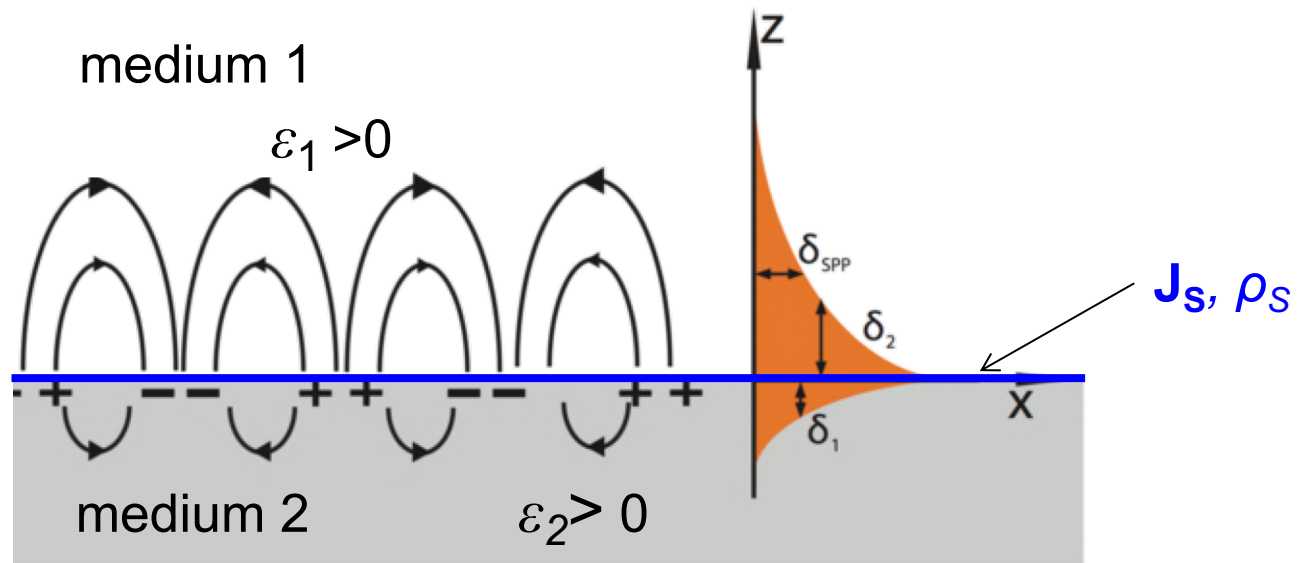
Surface plasmon polaritons in graphene

- Results presented so far assume that plasma oscillation in graphene is overdamped.
- When electron scattering rate ($1/\tau$) is low, **surface plasmon polaritons** may be excited, significantly improving interaction with radiation



Surface plasmon polaritons in graphene

- Collective surface charge oscillations coupled to light



- TM mode with exponentially decaying fields along z

- Boundary conditions: $E_{1x} = E_{2x}$

$$H_{1y} - H_{2y} = -J_x = -\sigma E_{2x}$$



Surface plasmon polaritons in graphene

- Boundary conditions yield:

$$\frac{\varepsilon_1}{\sqrt{\beta^2 - k_0^2 \varepsilon_1}} + \frac{\varepsilon_2}{\sqrt{\beta^2 - k_0^2 \varepsilon_2}} + \frac{i\sigma}{\omega \varepsilon_0} = 0$$

$$\sigma(\omega) = \frac{v_F e^2 \tau \sqrt{n_q}}{\hbar \sqrt{\pi} (1 - i\tau\omega)}$$

- For $\omega\tau \gg 1$

$$\frac{\varepsilon_1}{\sqrt{\beta^2 - k_0^2 \varepsilon_1}} + \frac{\varepsilon_2}{\sqrt{\beta^2 - k_0^2 \varepsilon_2}} = \frac{e^2 E_F}{\pi \varepsilon_0 (\hbar\omega)^2}$$

- In the electrostatic limit ($\beta^2 \gg k_0^2 \varepsilon_{1,2}$)

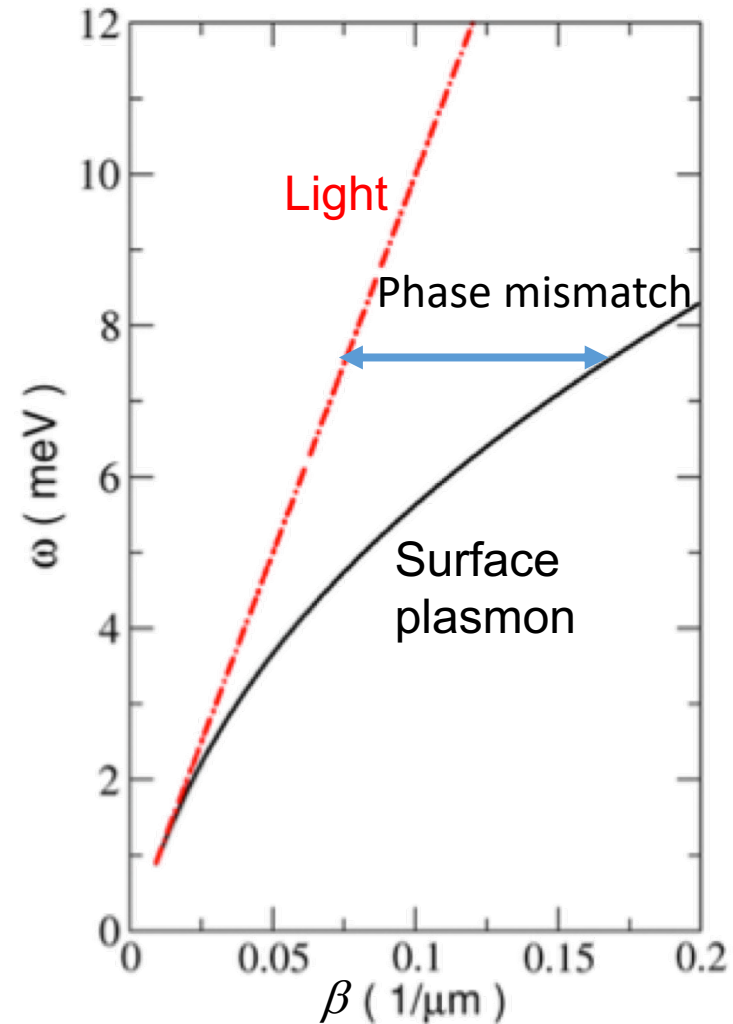
$$\hbar\omega_{pl} = \sqrt{\frac{e^2 E_F \beta}{2\pi \varepsilon_0 \bar{\varepsilon}}} \quad \bar{\varepsilon} = \frac{\varepsilon_1 + \varepsilon_2}{2}$$



Surface plasmon polaritons in graphene



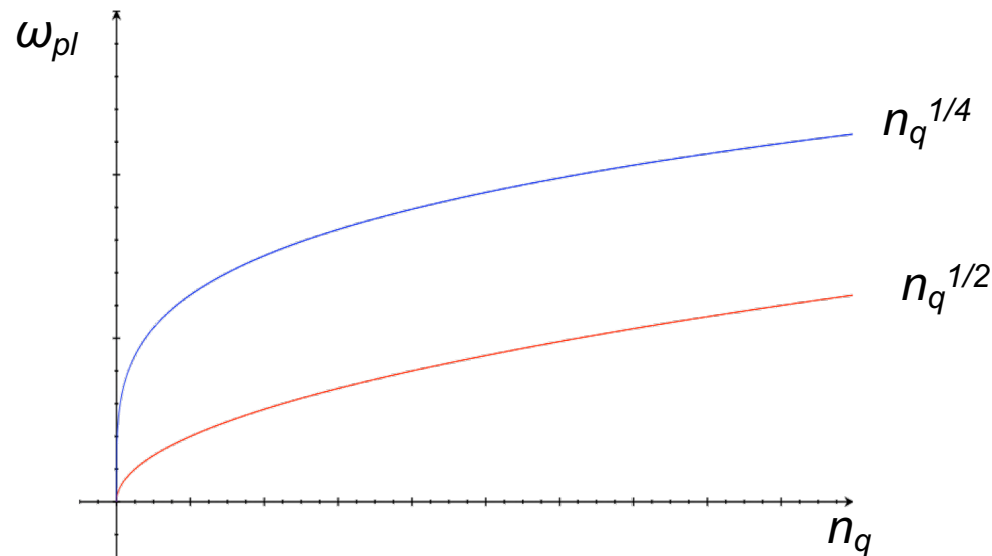
$$\hbar\omega_{pl} = \sqrt{\frac{e^2 E_F \beta}{2\pi\epsilon_0 \bar{\epsilon}}}$$





Surface plasmon polaritons in graphene

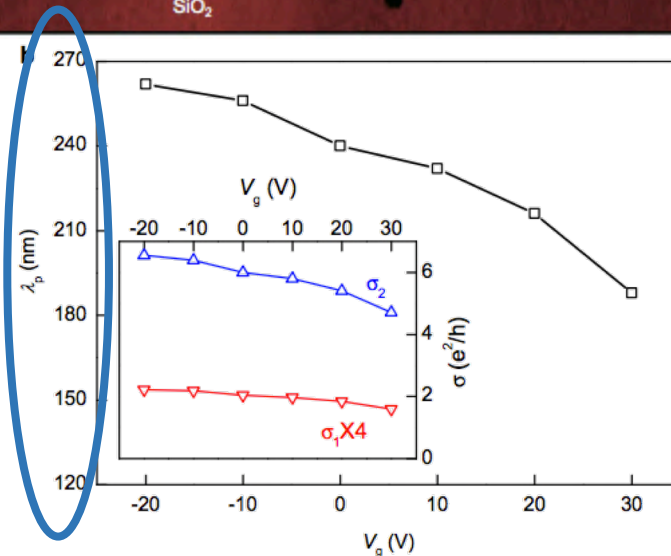
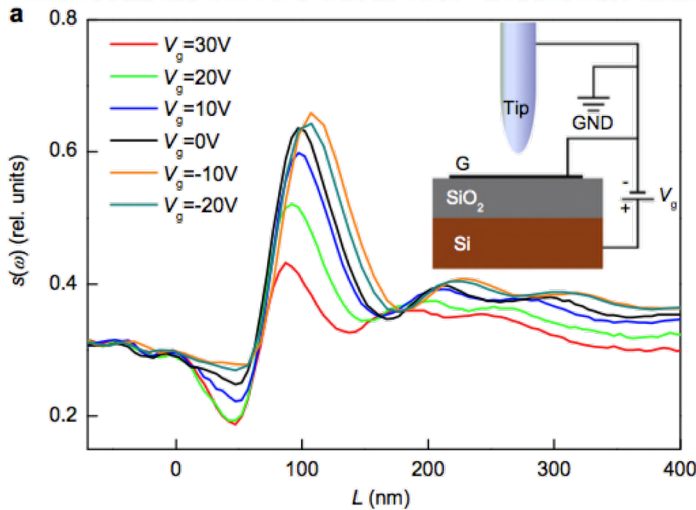
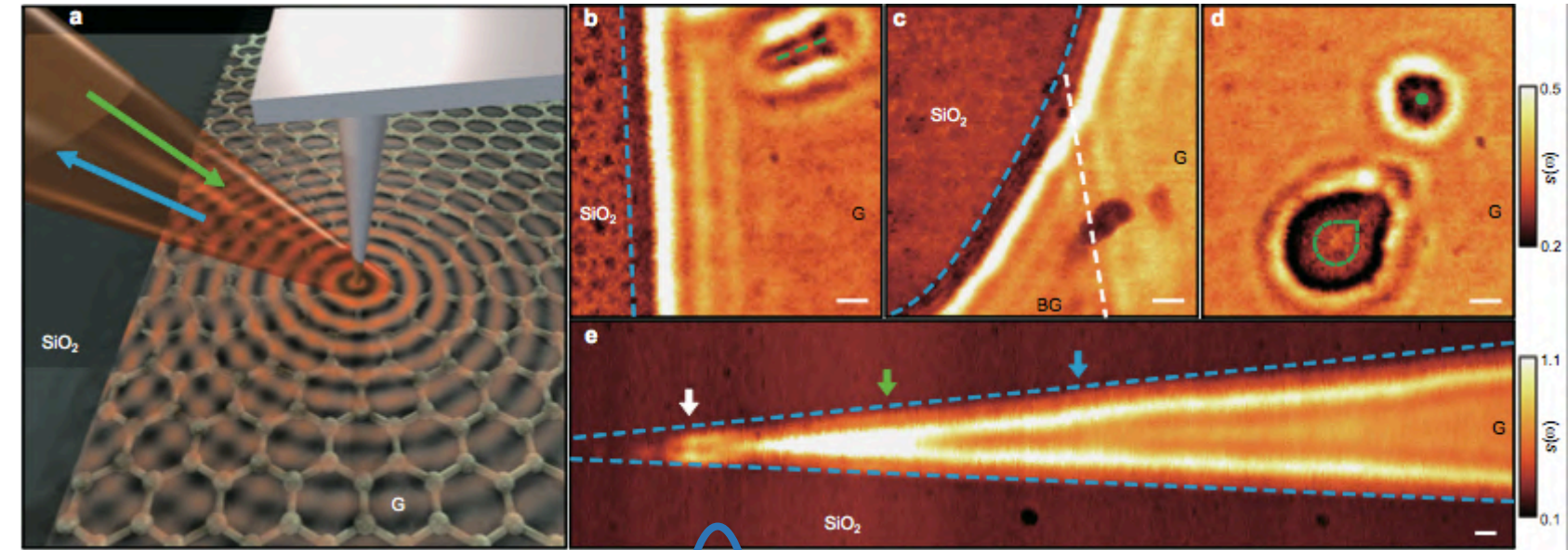
- For graphene: $E_F \propto \sqrt{n_q}$
- For parabolic materials: $E_F \propto n_q$
- $\rightarrow \omega_{pl} \propto n_q^{1/4} \beta^{1/2}$ (graphene)
 $\omega_{pl} \propto n_q^{1/2} \beta^{1/2}$ (parabolic 2D)



Much more ω_{pl} tunability in graphene



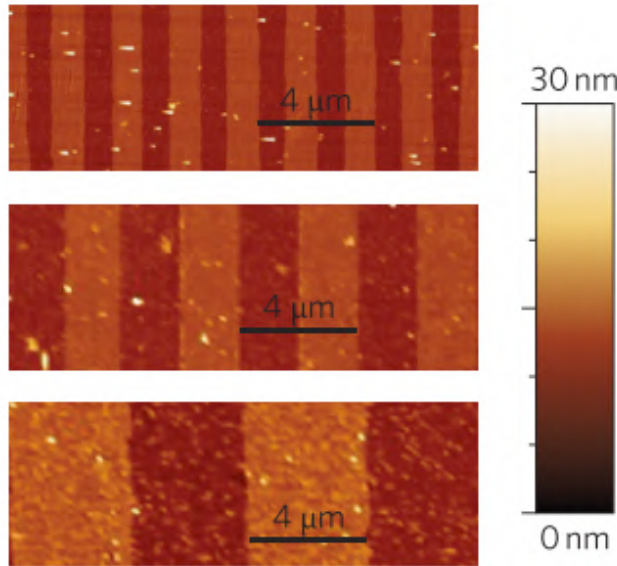
Surface plasmon polaritons in graphene



$$\lambda_{IR}/\lambda_p = 50-60$$

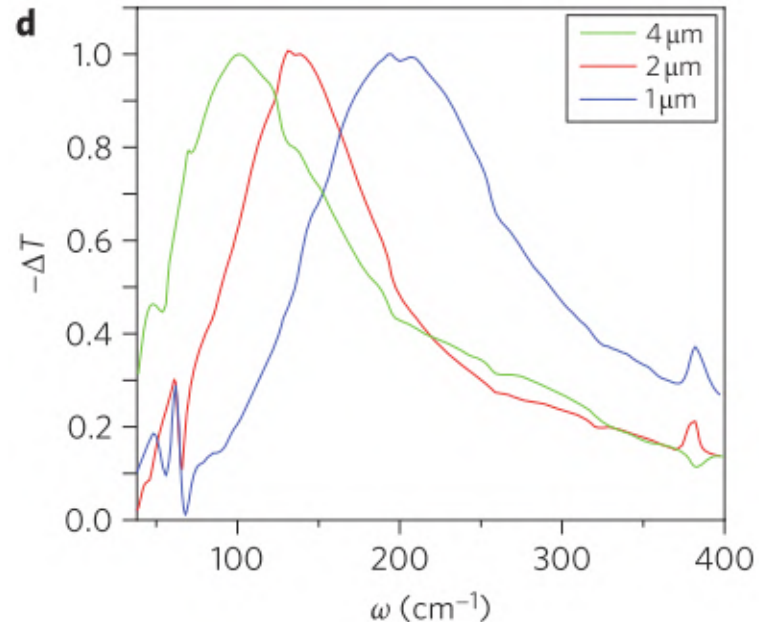
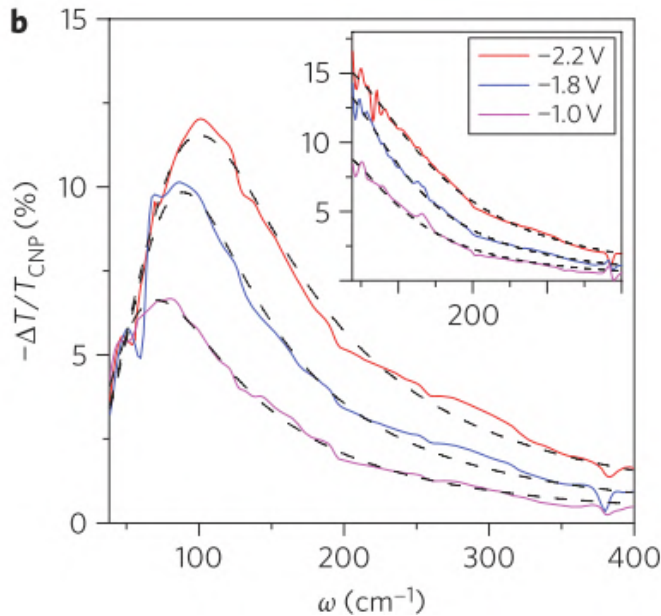


Localized surface plasmons in graphene



- The other way to overcome phase mismatch is to excite localized plasmons in micro/nanostructured graphene

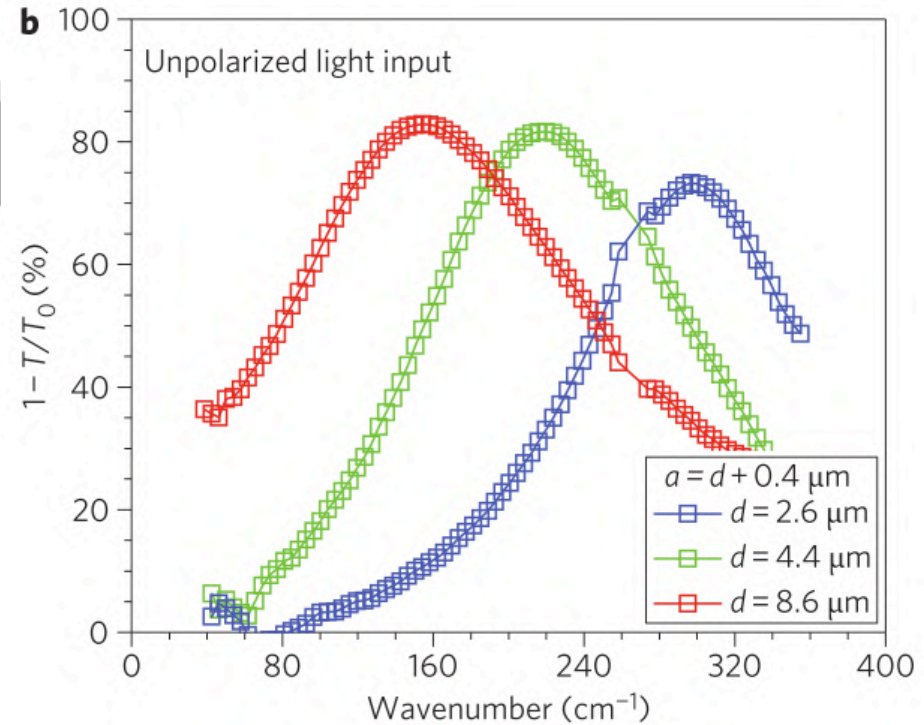
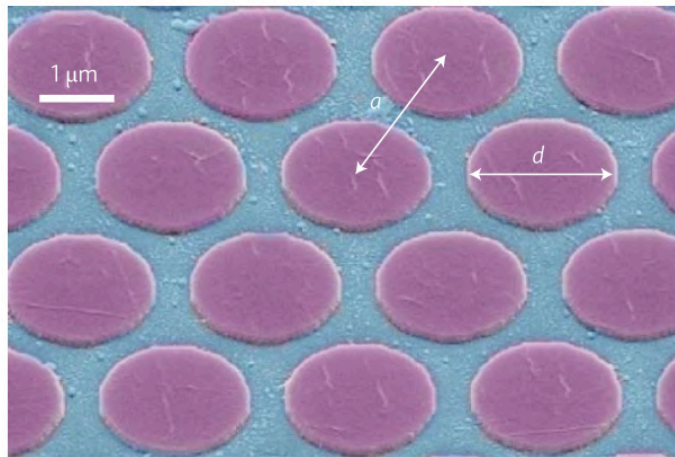
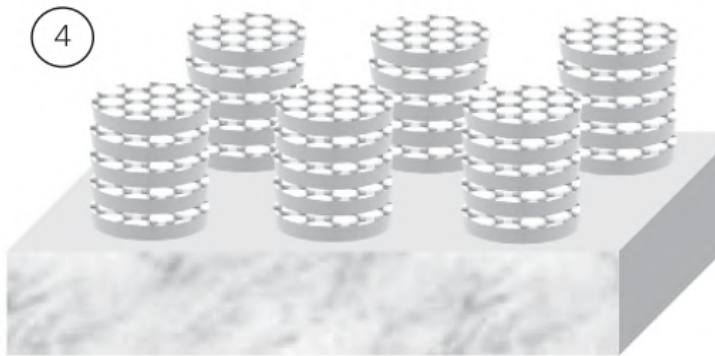
1.5 – 12 THz





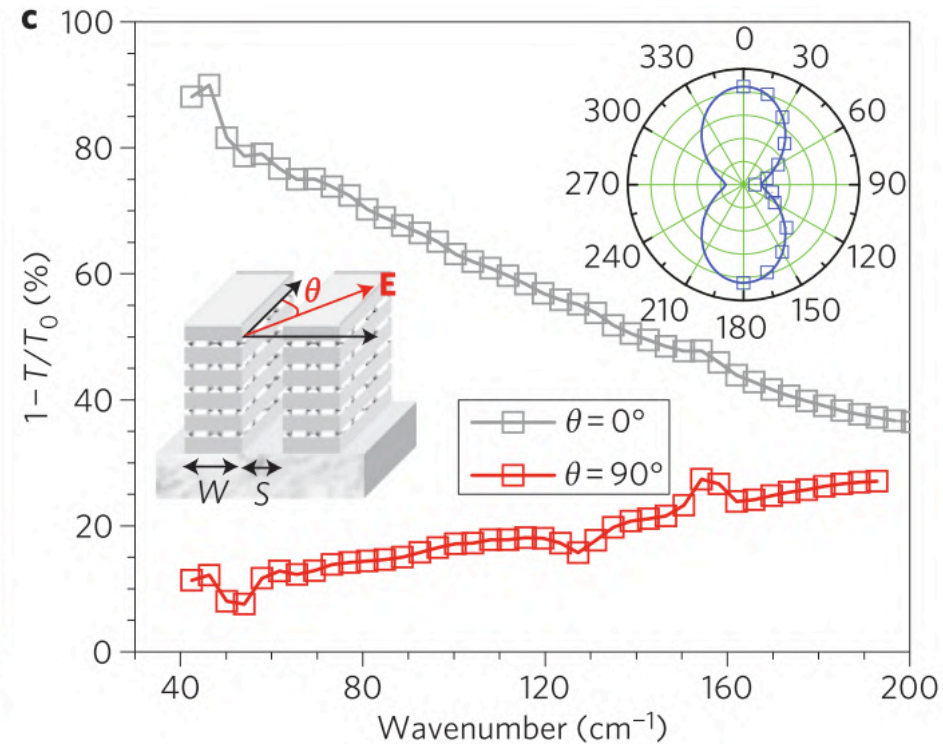
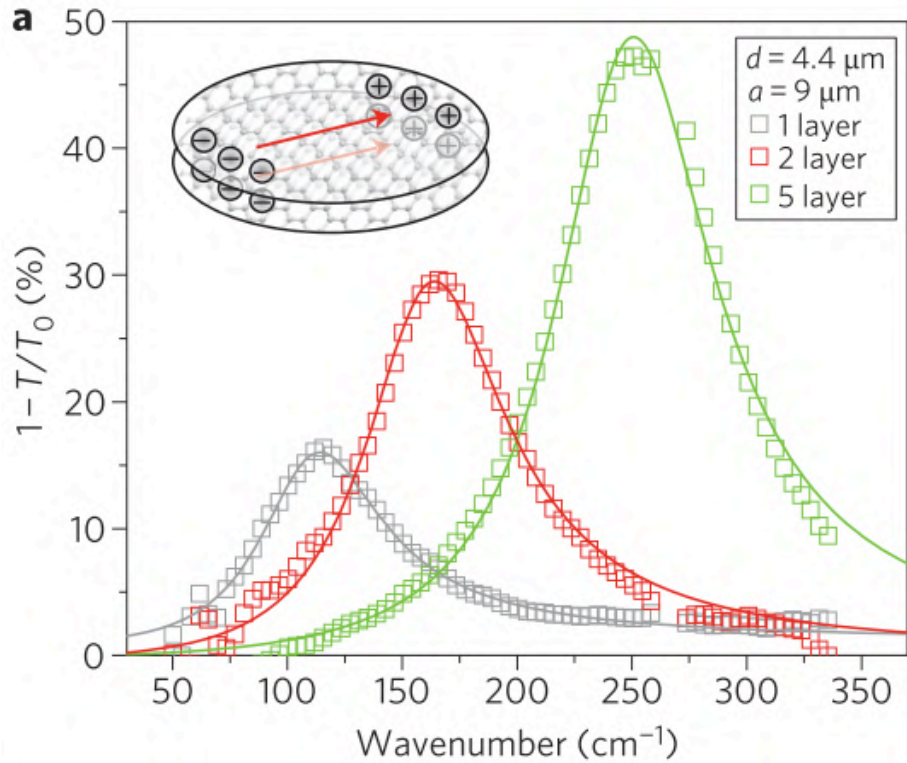
Filters/polarizers based on localized surface plasmons

- Multiple doped graphene monolayers
- 8.2 dB polarization indep. rejection





Filters/polarizers based on localized surface plasmons



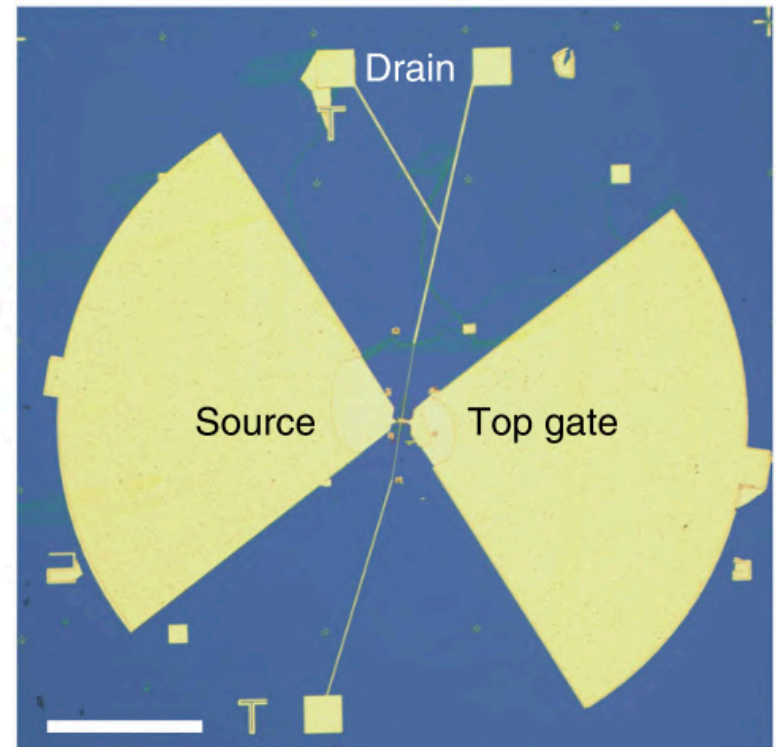
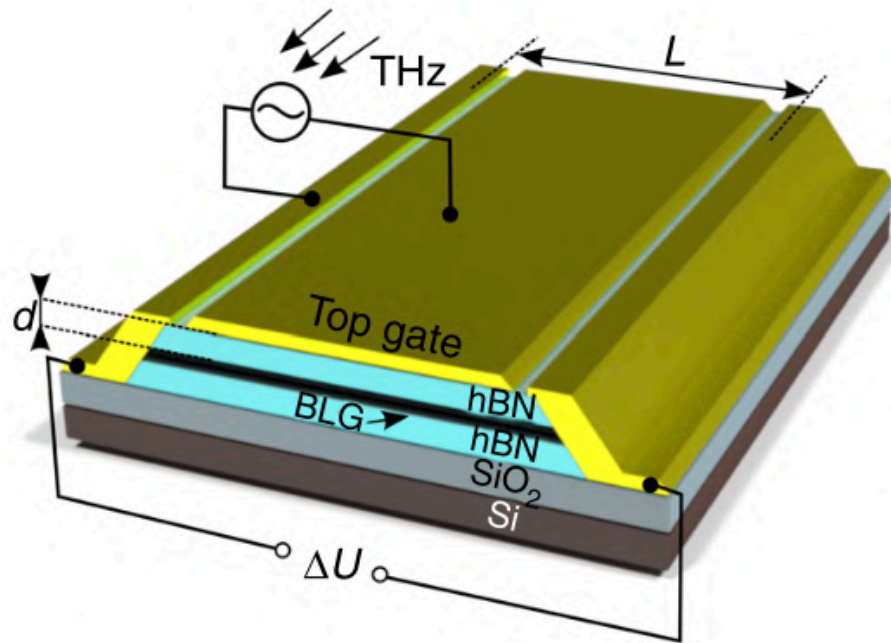
- Interlayer Coulomb interaction tunes filter

- 9.5 dB polarization extinction ratio



A resonant plasmonic detector

- Graphene bilayer FET
- FET acts as a plasmonic cavity and a rectifying element

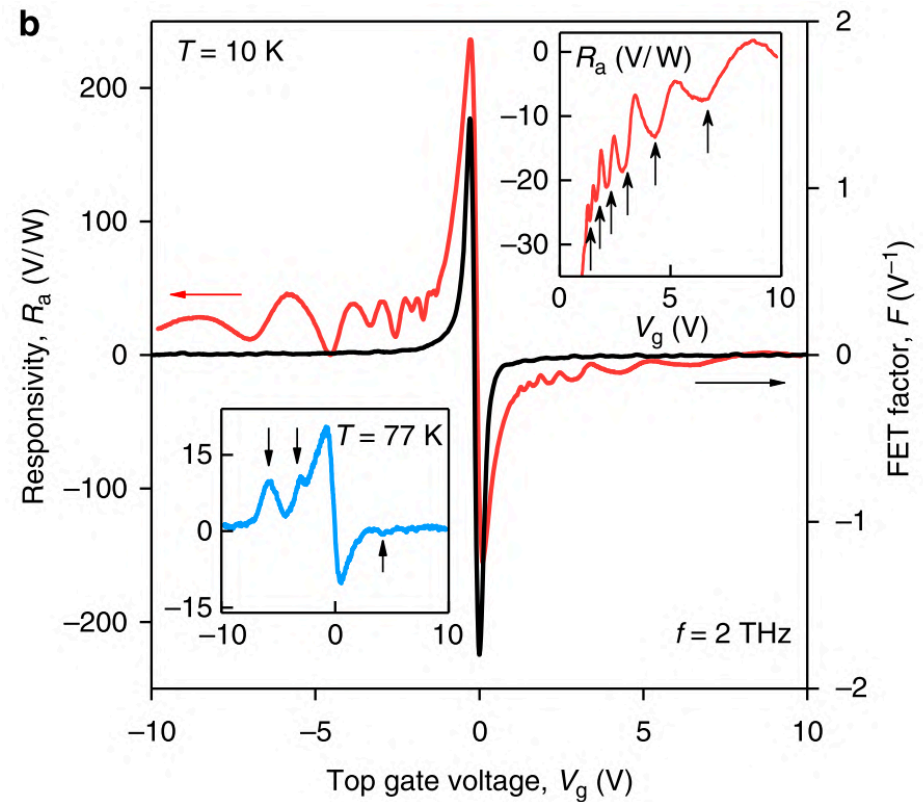
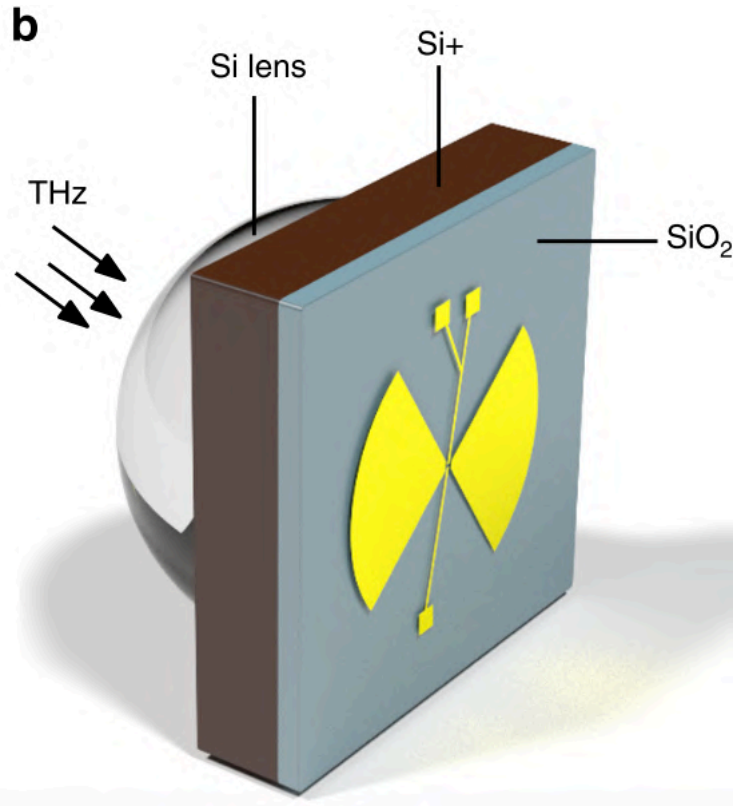




A resonant plasmonic detector



- Resonant peaks:
 - correspond to plasmonic Fabry-Perot modes
 - can be exploited to obtain spectral resolution





Conclusions and outlook

- Graphene present electronic, optoelectronic and plasmonic properties that make it attractive for THz applications
- The high charge mobility, electrical tunability and low temperature dependence are attractive features for use in astronomical instruments
- For space-bourne applications susceptibility to the space environment (e.g. cosmic rays, radiation) is yet to be further tested.



MackGraphe

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